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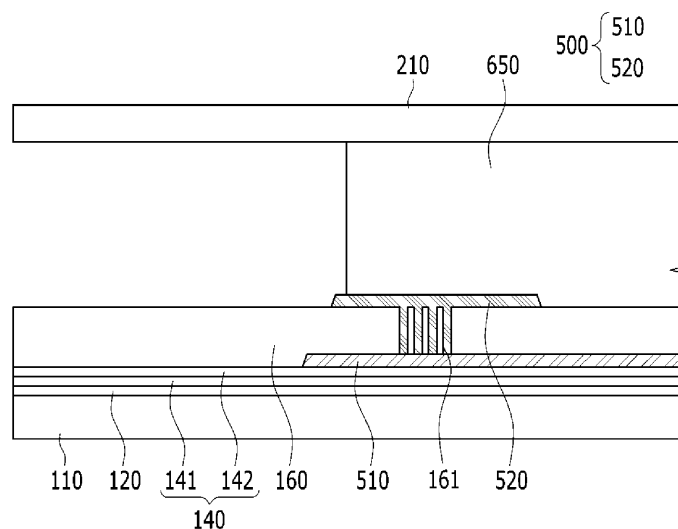
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(54) **ORGANIC LIGHT EMITTING DIODE DISPLAY DEVICE**

(57) An organic light emitting device includes a first substrate (110) including a display area and a non-display area, and a dummy metal layer (500) disposed on the first substrate in the non-display area. The dummy metal layer includes a first dummy metal layer (510) and a second dummy metal layer (520) that overlap each other. The organic light emitting device further includes an insulating layer (160) disposed between the first dum-

my metal layer and the second dummy metal layer in a cross-sectional view, a second substrate (210) covering the first substrate, and a sealant (650) disposed between the first substrate and the second substrate and overlapping the dummy metal layer. The first dummy metal layer is electrically connected to the second dummy metal layer, and the sealant contacts the second dummy metal layer.

FIG. 3



EP 3 232 489 A1

DescriptionTECHNICAL FIELD

[0001] Embodiments of the present invention relate to an organic light emitting device, and more particularly, to an organic light emitting device in which a sealant is prevented from peeling off of a substrate.

DISCUSSION OF THE RELATED ART

[0002] An organic light emitting diode display has a self-luminance characteristic and does not require a separate light source, unlike a liquid crystal display (LCD) device. As a result, an organic light emitting diode display may have a reduced thickness and weight. Further, the organic light emitting diode display has high-grade characteristics such as low power consumption, high luminance, a wide viewing angle, and a high response speed, making it a desirable choice for use in portable electronic devices.

[0003] In general, the organic light emitting device includes a first substrate on which thin film transistors and organic light emitting diodes are disposed, a second substrate covering the first substrate, and a sealant combining the first substrate and the second substrate. The sealant may be applied to edges of the first substrate and the second substrate, and seals a space between the first substrate and the second substrate.

[0004] The substrate includes a display area in which images are displayed and a non-display area in which a driver for driving the display area is disposed. The sealant is disposed in the non-display area. To improve adherence between the sealant and the substrate, a dummy metal layer may be disposed in the non-display area. Recently, according to a trend of reducing an area of the non-display area, an area of the dummy metal layer is also reduced and resistance of the dummy metal layer is increased. As a result, when static electricity occurs, charges are stored in the dummy metal layer, heat is generated, and the sealant may be stripped off of the substrate.

SUMMARY

[0005] According to an embodiment of the present invention, an organic light emitting device includes a first substrate including a display area and a non-display area, and a dummy metal layer disposed on the first substrate in the non-display area. The dummy metal layer includes a first dummy metal layer and a second dummy metal layer overlapping each other in a cross-sectional view. The organic light emitting device further includes an insulating layer disposed between the first dummy metal layer and the second dummy metal layer, a second substrate covering the first substrate, and a sealant disposed between the first substrate and the second substrate and overlapping the dummy metal layer. The first

dummy metal layer is electrically connected to the second dummy metal layer, and the sealant contacts the second dummy metal layer.

[0006] In an embodiment of the invention, the insulating layer includes a first contact hole overlapping at least a part of the first dummy metal layer, and the second dummy metal layer is disposed on the insulating layer and is connected to the first dummy metal layer through the first contact hole.

[0007] In an embodiment of the invention, a resistivity of the second dummy metal layer is less than a resistivity of the first dummy metal layer.

[0008] In an embodiment of the invention, the first dummy metal layer is made of molybdenum, and the second dummy metal layer is made of aluminum.

[0009] In an embodiment of the invention, the organic light emitting device further includes a semiconductor disposed on the first substrate in the display area, a gate insulating layer disposed on the semiconductor, and a gate wire disposed on the gate insulating layer. The insulating layer is disposed on the gate wire. The organic light emitting device further includes a data wire disposed on the insulating layer.

[0010] In an embodiment of the invention, the first dummy metal layer is made of a same material as the gate wire and is provided in a same layer as the gate wire.

[0011] In an embodiment of the invention, the gate insulating layer includes a first gate insulating layer and a second gate insulating layer, and the gate wire includes a first gate wire disposed between the first gate insulating layer and the second gate insulating layer in a cross-sectional view, and a second gate wire disposed on the second gate insulating layer.

[0012] In an embodiment of the invention, the first dummy metal layer is made of a same material as the first gate wire or the second gate wire, and is disposed in a same layer as the first gate wire or the second gate wire.

[0013] In an embodiment of the invention, the second dummy metal layer is made of a same material as the data wire, and is disposed in a same layer as the data wire.

[0014] In an embodiment of the invention, the first dummy metal layer and the second dummy metal layer have a bar shape extending substantially parallel to an edge of the first substrate.

[0015] In an embodiment of the invention, a width of the second dummy metal layer is less than a width of the first dummy metal layer in a plan view.

[0016] In an embodiment of the invention, a first edge of the second dummy metal layer includes a first plurality of protrusions and depressions.

[0017] In an embodiment of the invention, the first edge of the second dummy metal layer is adjacent to the edge of the first substrate.

[0018] In an embodiment of the invention, a second edge of the second dummy metal layer that opposes the first edge of the dummy metal layer includes a second plurality of protrusions and depressions.

[0019] In an embodiment of the invention, a hole pattern is formed in the first dummy metal layer, a second contact hole is formed in the insulating layer, and the second contact hole is disposed in the hole pattern.

[0020] In an embodiment of the invention, the sealant is disposed in the second contact hole.

[0021] In an embodiment of the invention, the sealant contacts the first substrate through the second contact hole.

[0022] In an embodiment of the invention, a plurality of second contact holes is provided in the hole pattern.

[0023] In an embodiment of the invention, a plurality of hole patterns is disposed in a matrix form in the first dummy metal layer.

[0024] In an embodiment of the invention, the second dummy metal layer does not overlap the hole pattern.

[0025] In an embodiment of the invention, a first edge of the second dummy metal layer adjacent to the edge of the first substrate, and a second edge of the second dummy metal layer that opposes the first edge of the second dummy metal layer each comprise a plurality of protrusions and depressions.

[0026] In an embodiment of the invention, the insulating layer includes a first contact hole and a third contact hole overlapping at least a part of the first dummy metal layer, the second dummy metal layer is connected to the first dummy metal layer through the first contact hole, and the sealant contacts the first dummy metal layer through the third contact hole.

[0027] According to an embodiment of the present invention, an organic light emitting device includes a first substrate including a display area and a non-display area, a second substrate opposing the first substrate, and a pixel disposed on the first substrate in the display area. The pixel includes a storage capacitor, an organic light emitting diode including an anode and a cathode, a driving transistor including a first gate electrode, and a switching transistor including a second gate electrode. The organic light emitting device further includes a dummy metal layer disposed on the first substrate in the non-display area. The dummy metal layer includes a first dummy metal layer and a second dummy metal layer. The first dummy metal layer and the second dummy metal layer overlap each other. The organic light emitting device further includes an insulating layer disposed on the first substrate in the non-display area between the first dummy metal layer and the second dummy metal layer in a cross-sectional view, and a sealant disposed on the first substrate in the non-display area between the first substrate and the second substrate, and overlapping the dummy metal layer. The first dummy metal layer, the first gate electrode, and the second gate electrode are made of a same material.

[0028] In an embodiment of the invention, the first gate electrode is connected to a first end of the storage capacitor, a second end of the storage capacitor is connected to a driving voltage line, the second gate electrode is connected to a scan line, the anode is connected to a

drain electrode of the driving transistor, and the cathode is connected to a common voltage line.

[0029] In an embodiment of the invention, the insulating layer includes a first contact hole overlapping at least a part of the first dummy metal layer, and the second dummy metal layer is disposed on the insulating layer and is connected to the first dummy metal layer through the first contact hole.

[0030] In an embodiment of the invention, a resistivity of the second dummy metal layer is less than a resistivity of the first dummy metal layer.

[0031] In an embodiment of the invention, the first dummy metal layer is made of molybdenum, and the second dummy metal layer is made of aluminum.

BRIEF DESCRIPTION OF THE DRAWINGS

[0032] The above and other features of the present invention will be made more apparent by describing in detail embodiments thereof with reference to the accompanying drawings, in which:

FIG. 1 shows a top plan view of an organic light emitting device according to an embodiment of the present invention.

FIG. 2 shows a top plan view of an enlarged portion A of FIG. 1 of an organic light emitting device according to an embodiment of the present invention. FIG. 3 shows a cross-sectional view of an organic light emitting device with respect to line III-III of FIG. 2 according to an embodiment of the present invention.

FIG. 4 shows an equivalent circuit diagram of one pixel of an organic light emitting device according to an embodiment of the present invention.

FIG. 5 shows a layout view of a plurality of transistors and capacitors of an organic light emitting device according to an embodiment of the present invention.

FIG. 6 shows a detailed layout view of FIG. 5 according to an embodiment of the present invention.

FIG. 7 shows a cross-sectional view of the organic light emitting device of FIG. 6 with respect to line VII-VII according to an embodiment of the present invention.

FIG. 8 shows a cross-sectional view of the organic light emitting device of FIG. 6 with respect to line VIII-VIII according to an embodiment of the present invention.

FIG. 9 shows a cross-sectional view of an organic light emitting device according to an embodiment of the present invention.

FIG. 10 shows a top plan view of an organic light emitting device according to an embodiment of the present invention.

FIG. 11 shows a top plan view of an organic light emitting device according to an embodiment of the present invention.

FIG. 12 shows a cross-sectional view of an organic light emitting device according to an embodiment with respect to line XII-XII of FIG. 11.

FIG. 13 shows a cross-sectional view of an organic light emitting device according to an embodiment of the present invention.

FIG. 14 shows a top plan view of an organic light emitting device according to an embodiment of the present invention.

FIG. 15 shows a top plan view of an organic light emitting device according to an embodiment of the present invention.

FIG. 16 shows a cross-sectional view of an organic light emitting device according to an embodiment with respect to line XVI-XVI of FIG. 15.

FIG. 17 shows a cross-sectional view of an organic light emitting device according to an embodiment of the present invention.

FIG. 18 shows a top plan view of an organic light emitting device according to an embodiment of the present invention.

DETAILED DESCRIPTION

[0033] Embodiments of the present invention will be described more fully hereinafter with reference to the accompanying drawings. Like reference numerals may refer to like elements throughout the accompanying drawings.

[0034] It will be understood that when a component, such as a film, a region, a layer, or an element, is referred to as being "on", "connected to", "coupled to", or "adjacent to" another component, it can be directly on, connected, coupled, or adjacent to the other component, or intervening components may be present. It will also be understood that when a component is referred to as being "between" two components, it can be the only component between the two components, or one or more intervening components may also be present. It will also be understood that when a component is referred to as "covering" another component, it can be the only component covering the other component, or one or more intervening components may also be covering the other component. Further, when a first area or component is described as surrounding a second area or component, it is to be understood that the first area or component may entirely or partially surround the second area or component.

[0035] It will further be understood that the terms "first," "second," "third," etc. are used herein to distinguish one element from another, and the elements are not limited by these terms. Thus, a "first" element in an embodiment may be described as a "second" element in another embodiment.

[0036] It will be further understood that when two components or directions are described as extending substantially parallel or perpendicular to each other, the two components or directions extend exactly parallel or perpendicular to each other, or extend approximately paral-

lel or perpendicular to each other as would be understood by a person having ordinary skill in the art. Further, when two or more components or values are described as being substantially the same as or about equal to each other, it is to be understood that the components or values are identical to each other, indistinguishable from each other, or distinguishable from each other but functionally the same as each other as would be understood by a person having ordinary skill in the art. Further, when two processes are described as being performed simultaneously or at substantially the same time as each other, it is to be understood that the processes may be performed at exactly the same time or at about the same time as would be understood by a person having ordinary skill in the art.

[0037] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIG. 1.

[0038] FIG. 1 shows a top plan view of an organic light emitting device according to an embodiment of the invention.

[0039] As shown in FIG. 1, the organic light emitting device includes a first substrate 110, a second substrate 210, and a sealant 650 provided between the first substrate 110 and the second substrate 210.

[0040] The first substrate 110 and the second substrate 210 may be made of an insulating material such as, for example, glass, quartz, ceramic, or plastic.

[0041] The first substrate 110 includes a display area (DA) in which a screen is disposed and an image is displayed, and a non-display area (NA) in which a driver for driving the display area (DA) is disposed. The non-display area (NA) surrounds the display area (DA). For example, the display area (DA) is disposed near a center of the first substrate 110, and the non-display area (NA) is disposed near an edge of the first substrate 110. Thin film transistors and organic light emitting diodes may be disposed in the display area (DA). The organic light emitting diodes may emit light for the respective pixels to display the image. A gate driver and a data driver that transmit predetermined signals for driving the display area (DA) are disposed in the non-display area (NA).

[0042] A dummy metal layer 500 is disposed in the non-display area (NA) of the first substrate 110. The dummy metal layer 500 surrounds part of the edge of the first substrate 110. The first substrate 110 may substantially form a rectangle, and the dummy metal layer 500 may be formed on three of four sides that form the rectangle. A fan-out portion 129 may be formed on the side on which the dummy metal layer 500 is not disposed. The dummy metal layer 500 may be disposed on a same layer as the fan-out portion 129 with a same metal material. Therefore, the dummy metal layer 500 and the fan-out portion 129 are provided at different positions so that they are not short-circuited.

[0043] The second substrate 210 is attached to the first substrate 110. The second substrate 210 may function as an encapsulation substrate for preventing moisture

from permeating into a space between the first substrate 110 and the second substrate 210. The second substrate 210 may have a similar shape to that of the first substrate 110 and may be smaller than the first substrate 110. Therefore, part of the first substrate 110 may not be covered by the second substrate 210. For example, part of the first substrate 100 on which part of the fan-out portion 129 is disposed may be a portion that is not covered by the second substrate 210, as shown in FIG. 1.

[0044] The dummy metal layer 500 may extend to an end portion of the first substrate 110 near the fan-out portion 129. That is, the dummy metal layer 500 may extend to the end portion of the first substrate 110 in the portion where the first substrate 110 is not covered by the second substrate 210.

[0045] The sealant 650 is disposed in the non-display area (NA) of the first substrate 110 and overlaps the dummy metal layer 500. The sealant 650 may surround the edge (e.g., the entire edge) of the first substrate 110. That is, when the first substrate 110 forms a rectangle, the sealant 650 may be disposed on all four sides of the rectangle.

[0046] The sealant 650 may be made of a frit. When a glass material is heated at a high temperature and the temperature is manipulated to steeply decrease, a frit of a glass powder type is formed. When an oxide powder is added to the powder type frit and an organic material is added thereto, a paste in a gel state is formed. When the paste is applied to an edge of the second substrate 210 and is heated at a predetermined temperature, the organic material dissipates into the air, the paste in the gel state is hardened, and the sealant 650, which is now a solid frit, is attached to the second substrate 210. When a side of the second substrate 210 to which the sealant 650 is attached is disposed such that it contacts the first substrate 110, and laser beams or infrared rays are irradiated thereto, the sealant 650 is melted and attached to the first substrate 110, and the first substrate 110 is bonded to the second substrate 210. When the first substrate 110 is bonded to the second substrate 210 by the sealant 650, oxygen or moisture may be prevented from permeating into the space between the first substrate 110 and the second substrate 210. Therefore, the organic light emitting diode disposed in the display area (DA) of the first substrate 110 may be prevented from being exposed to the oxygen or moisture, thus preventing the organic light emitting diode from being damaged.

[0047] A configuration of the non-display area (NA) of the organic light emitting device according to an embodiment of the invention will now be described with reference to FIGs. 2 and 3.

[0048] FIG. 2 shows a top plan view of an enlarged portion A of FIG. 1 of an organic light emitting device according to an exemplary embodiment. FIG. 3 shows a cross-sectional view of an organic light emitting device with respect to line III-III of FIG. 2 according to an embodiment of the invention. The portion A in FIG. 1 corresponds to the non-display area (NA).

[0049] As shown in FIGs. 2 and 3, a buffer layer 120 may be disposed on the first substrate 110, and a gate insulating layer 140 may be disposed on the buffer layer 120.

[0050] The buffer layer 120 may be made of an inorganic insulating material such as, for example, a silicon nitride (SiNx) or a silicon oxide (SiOx). The buffer layer 120 may be formed of a single layer or multiple layers. The buffer layer 120 may prevent permeation of unnecessary components such as, for example, impurities or moisture, and substantially simultaneously flattens the surface. The buffer layer 120 may be disposed in the display area (DA) as well as the non-display area (NA) of the first substrate 110. Thus, the buffer layer 120 may be disposed on the entire side of the first substrate 110.

[0051] The gate insulating layer 140 may be made of an inorganic insulating material such as, for example, a silicon nitride (SiNx) or a silicon oxide (SiOx). The gate insulating layer 140 may be formed of a single layer or multiple layers. For example, the gate insulating layer 140 may include a first gate insulating layer 141 and a second gate insulating layer 142 disposed on the first gate insulating layer 141. The gate insulating layer 140 may be disposed in the display area (DA) as well as the non-display area (NA) of the first substrate 110. Thus, the gate insulating layer 140 may be disposed on the entire side of the first substrate 110.

[0052] Although the buffer layer 120 and the gate insulating layer 140 have been described above as being disposed on the entire side of the first substrate 110, the present invention is not limited thereto. For example, in an embodiment, the buffer layer 120 and the gate insulating layer 140 are not formed in the non-display area (NA) of the first substrate 110.

[0053] The dummy metal layer 500 is disposed on the gate insulating layer 140. The dummy metal layer 500 may be disposed on the second gate insulating layer 142. The dummy metal layer 500 may include a first dummy metal layer 510 and a second dummy metal layer 520. The first dummy metal layer 510 may overlap the second dummy metal layer 520. An interlayer insulating layer 160 may be disposed between the first dummy metal layer 510 and the second dummy metal layer 520.

[0054] The interlayer insulating layer 160 may be made of an inorganic insulating material or an organic insulating material. The interlayer insulating layer 160 may be configured with a single layer or multiple layers. The interlayer insulating layer 160 may be disposed by stacking a layer made of an organic insulating material and a layer made of an inorganic insulating material. The interlayer insulating layer 160 may be disposed in the display area (DA) as well as the non-display area (NA) of the first substrate 110. Thus, the interlayer insulating layer 160 may be disposed on the entire side of the first substrate 110.

[0055] The first dummy metal layer 510 may be disposed on the second gate insulating layer 142, and the interlayer insulating layer 160 may be disposed on the

first dummy metal layer 510. A first contact hole 161 overlapping at least part of the first dummy metal layer 510 is disposed in the interlayer insulating layer 160. The first contact hole 161 may be disposed in a matrix form in a horizontal direction and a vertical direction on the plane. For example, as shown in FIG. 2, in an embodiment, sixteen first contact holes 161 disposed in a 4x4 matrix may form one set, and a plurality of sets of the first contact holes 161 may be disposed in a column direction with a predetermined gap therebetween. However, the form of the first contact hole 161, and the amount of first contact holes 161 that form each set and that are included in the organic light emitting device are not limited thereto.

[0056] The second dummy metal layer 520 may be disposed on the interlayer insulating layer 160. The second dummy metal layer 520 is disposed in the first contact hole 161 and is connected to the first dummy metal layer 510 through the first contact hole 161. Therefore, the first dummy metal layer 510 is electrically connected to the second dummy metal layer 520. The resistivity of the second dummy metal layer 520 may be less than the resistivity of the first dummy metal layer 510. For example, the first dummy metal layer 510 may include molybdenum, and the second dummy metal layer 520 may include titanium or aluminum. The first dummy metal layer 510 may be formed of a single layer of molybdenum. The second dummy metal layer 520 may be formed of three layers including titanium, aluminum, and titanium.

[0057] The sealant 650 is disposed on the second dummy metal layer 520, and the second dummy metal layer 520 contacts (e.g., directly contacts) the sealant 650. When static electricity is applied to the sealant 650, most of the charges may be dispersed to the dummy metal layer 500 since the sealant 650 contacts the dummy metal layer 500, which is made of a metal material. The dummy metal layer 500 includes the first dummy metal layer 510 and the second dummy metal layer 520, which are electrically connected to each other. As a result, resistance of the dummy metal layer 500 when it includes the first and second dummy metal layers 510 and 520 connected to each other may be lower than a case in which the dummy metal layer 500 is formed as a single layer. For example, the dummy metal layer 500 further includes the second dummy metal layer 520 with relatively less resistivity than a case in which the dummy metal layer 500 is formed with the first dummy metal layer 510 with relatively greater resistivity, further lowering the resistance. As described, when the resistance of the dummy metal layer 500 contacting the sealant 650 is reduced, the dispersing effect of charges becomes greater, and the sealant 650 may be prevented from being separated from the first substrate 110 by the static electricity.

[0058] The second substrate 210 is disposed on the sealant 650. The sealant 650 is formed along the edge between the first substrate 110 and second substrate 210. As a result, moisture may be prevented from permeating into the space between the first substrate 110

and the second substrate 210.

[0059] In an embodiment, the first dummy metal layer 510 and the second dummy metal layer 520 may have a bar shape extending substantially parallel to the edge of the first substrate 110. For example, the first dummy metal layer 510 and the second dummy metal layer 520 may extend lengthwise in a direction substantially parallel to that in which the edge of the first substrate 110 extends. A width of the second dummy metal layer 520 may be less than a width of the first dummy metal layer 510 (e.g., a width of the second dummy metal layer 520 may be narrower than a width of the first dummy metal layer 510 in a plan view, as shown in FIG. 2). In an exemplary embodiment, the entire second dummy metal layer 520 may overlap part of the first dummy metal layer 510. The second dummy metal layer 520 may overlap an edge portion of the first dummy metal layer 510. For example, the second dummy metal layer 520 may overlap the edge portion of the first dummy metal layer 510 disposed near the edge of the first substrate 110. Static electricity may be transmitted through an outer portion of the sealant 650. Thus, the second dummy metal layer 520 may be disposed at a position that is nearest the edge of the first substrate 110 when static electricity is dispersed.

[0060] Although an embodiment of the invention has been described in which a width of the second dummy metal layer 520 is less than a width of the first dummy metal layer 510, resulting in the second dummy metal layer 520 overlapping part of the first dummy metal layer 510, the present invention is not limited thereto. For example, in an embodiment, the width of the second dummy metal layer 520 may substantially correspond to the width of the first dummy metal layer 510 (e.g., the widths of the first and second dummy metal layers 510 and 520 may be substantially equal), and the second dummy metal layer 520 may overlap the entire first dummy metal layer 510.

[0061] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIGs. 4 to 8.

[0062] FIG. 4 shows an equivalent circuit diagram of one pixel of an organic light emitting device according to an embodiment of the invention.

[0063] As shown in FIG. 4, the organic light emitting device includes a plurality of signal lines 151, 152, 153, 171, 172, and 192, and a plurality of pixels PX connected to the signal lines and substantially arranged in a matrix form.

[0064] The respective pixels PX include a plurality of transistors T1, T2, T3, T4, T5, and T6 connected to the plurality of signal lines 151, 152, 153, 171, 172, and 192, a storage capacitor (Cst), and an organic light emitting diode (OLD).

[0065] The transistors T1, T2, T3, T4, T5, and T6 include a driving transistor T1, a switching transistor T2, a compensation transistor T3, an initialization transistor T4, an operation control transistor T5, and a light emission control transistor T6. The signal lines 151, 152, 153,

171, 172, and 192 include a scan line 151 for transmitting a scan signal (Sn), a previous-stage scan line 152 for transmitting a previous-stage scan signal Sn-1 to the initialization transistor T4, a light emission control line 153 for transmitting a light emission control signal (EM) to the operation control transistor T5 and the light emission control transistor T6, a data line 171 crossing the scan line 151 and transmitting a data signal (Dm), a driving voltage line 172 transmitting a driving voltage (ELVDD) and disposed substantially parallel to the data line 171, and an initialization voltage line 192 for transmitting an initialization voltage (Vint) for initializing the driving transistor T1.

[0066] The driving transistor T1 includes a gate electrode G1 connected to a first end Cst1 of the storage capacitor Cst, a source electrode S1 connected to the driving voltage line 172 via the operation control transistor T5, and a drain electrode D1 electrically connected to an anode of the organic light emitting diode (OLED) via the light emission control transistor T6. The driving transistor T1 receives the data signal (Dm) according to switching by the switching transistor T2, and supplies a driving current (Id) to the organic light emitting diode (OLED).

[0067] The switching transistor T2 includes a gate electrode G2 connected to the scan line 151, a source electrode S2 connected to the data line 171, and a drain electrode D2 connected to the source electrode S1 of the driving transistor T1 and to the driving voltage line 172 via the operation control transistor T5. The switching transistor T2 is turned on by the scan signal (Sn) provided through the scan line 151 to perform a switching operation for transmitting the data signal (Dm) provided through the data line 171 to the source electrode S1 of the driving transistor T1.

[0068] The compensation transistor T3 includes a gate electrode G3 connected to the scan line 151, a source electrode S3 connected to the drain electrode D1 of the driving transistor T1 and to the anode of the organic light emitting diode (OLED) via the light emission control transistor T6, and a drain electrode D3 connected to a drain electrode D4 of the initialization transistor T4, the first end Cst1 of the storage capacitor Cst, and the gate electrode G1 of the driving transistor T1. The compensation transistor T3 is turned on by the scan signal (Sn) provided through the scan line 151 to connect the gate electrode G1 and the drain electrode D1 of the driving transistor T1, resultantly diode-connecting the driving transistor T1.

[0069] The initialization transistor T4 includes a gate electrode G4 connected to the previous-stage scan line 152, a source electrode S4 connected to the initialization voltage line 192, and a drain electrode D4 connected to the first end Cst1 of the storage capacitor Cst and the gate electrode G1 of the driving transistor T1 through the drain electrode D3 of the compensation transistor T3. The initialization transistor T4 is turned on by a previous-stage scan signal Sn-1 provided through the previous-stage scan line 152 to transmit the initialization voltage (Vint) to the gate electrode G1 of the driving transistor

T1 and perform an initialization operation for initializing a gate voltage (Vg) at the gate electrode G1 of the driving transistor T1.

[0070] The operation control transistor T5 includes a gate electrode G5 connected to the light emission control line 153, a source electrode S5 connected to the driving voltage line 172, and a drain electrode D5 connected to the source electrode S1 of the driving transistor T1 and the drain electrode D2 of the switching transistor T2.

[0071] The light emission control transistor T6 includes a gate electrode G6 connected to the light emission control line 153, a source electrode S6 connected to the drain electrode D1 of the driving transistor T1 and the source electrode S3 of the compensation transistor T3, and a drain electrode D6 electrically connected to the anode of the organic light emitting diode (OLED). The operation control transistor T5 and the light emission control transistor T6 are substantially simultaneously turned on by a light emission control signal (EM) provided through the light emission control line 153, and the driving voltage (ELVDD) is compensated through the diode-connected driving transistor T1 and is transmitted to the organic light emitting diode (OLED).

[0072] The storage capacitor Cst includes a second end Cst2 connected to the driving voltage line 172, and the organic light emitting diode (OLED) includes a cathode connected to a common voltage line 741 for transmitting a common voltage (ELVSS).

[0073] A detailed configuration of an organic light emitting device according to an embodiment shown in FIG. 4 will now be described with reference to FIGs. 5, 6, 7, and 8.

[0074] FIG. 5 shows a layout view of a plurality of transistors and capacitors of an organic light emitting device according to an embodiment of the invention. FIG. 6 shows a detailed layout view of FIG. 5 according to an embodiment of the invention. FIG. 7 shows a cross-sectional view of the organic light emitting device of FIG. 6 with respect to line VII-VII according to an embodiment of the invention. FIG. 8 shows a cross-sectional view of the organic light emitting device of FIG. 6 with respect to line VIII-VIII according to an embodiment of the invention.

[0075] A detailed top plan view configuration of an organic light emitting device according to an embodiment of the invention will now be described with reference to FIGs. 5 and 6, and a cross-sectional configuration thereof will be described with reference to FIGs. 7 and 8.

[0076] The organic light emitting device includes the scan line 151, the previous-stage scan line 152, and the light emission control line 153 for applying the scan signal (Sn), the previous-stage scan signal (Sn-1), and the light emission control signal (EM), respectively. The scan line 151, the previous-stage scan line 152, and the light emission control line 153 are disposed in a row direction. The organic light emitting device includes the data line 171 and the driving voltage line 172 crossing the scan line 151, the previous-stage scan line 152, and the light emission control line 153, and respectively applying the data

signal (Dm) and the driving voltage (ELVDD) to the pixel PX. The initialization voltage (Vint) is transmitted to the compensation transistor T3 from the initialization voltage line 192 via the initialization transistor T4. The initialization voltage line 192 includes a linear portion and an oblique portion that are alternately arranged. For example, the initialization voltage line 192 may include a plurality of portions extending from one another at different angles.

[0077] Further, the pixel PX includes the driving transistor T1, the switching transistor T2, the compensation transistor T3, the initialization transistor T4, the operation control transistor T5, the light emission control transistor T6, the storage capacitor Cst, and the organic light emitting diode (OLD).

[0078] The organic light emitting diode (OLD) includes a pixel electrode 191, an organic emission layer 370, and a common electrode 270.

[0079] Each channel of the driving transistor T1, the switching transistor T2, the compensation transistor T3, the initialization transistor T4, the operation control transistor T5, and the light emission control transistor T6 is formed in one connected semiconductor 130. The semiconductor 130 may be bent in various shapes. The semiconductor 130 may be made of, for example, polysilicon or an oxide semiconductor.

[0080] The channel 131 includes a driving channel 131a provided to the driving transistor T1, a switching channel 131b provided to the switching transistor T2, a compensation channel 131c provided to the compensation transistor T3, an initialization channel 131d provided to the initialization transistor T4, an operation control channel 131e provided to the operation control transistor T5, and a light emission control channel 131f provided to the light emission control transistor T6.

[0081] The driving transistor T1 includes the driving channel 131a, a driving gate electrode 155a, a driving source electrode 136a, and a driving drain electrode 137a. The driving gate electrode 155a overlaps the driving channel 131a, and the driving source electrode 136a and the driving drain electrode 137a are disposed on respective nearby sides of the driving channel 131a. The driving gate electrode 155a is connected to a first data connecting member 174 through a contact hole 61.

[0082] The switching transistor T2 includes the switching channel 131b, a switching gate electrode 155b, a switching source electrode 136b, and a switching drain electrode 137b. The switching gate electrode 155b that is part of a portion extending downward from the scan line 151 overlaps the switching channel 131b. The switching source electrode 136b and the switching drain electrode 137b are formed on respective nearby sides of the switching channel 131b. The switching source electrode 136b is connected to the data line 171 through a contact hole 62.

[0083] The compensation transistor T3 includes the compensation channel 131c, a compensation gate electrode 155c, a compensation source electrode 136c, and

a compensation drain electrode 137c. The compensation gate electrode 155c which is part of the scan line 151 overlaps the compensation channel 131c. The compensation source electrode 136c and the compensation drain electrode 137c are disposed on respective nearby sides of the compensation channel 131c. The compensation drain electrode 137c is connected to the first data connecting member 174 through a contact hole 63.

[0084] The initialization transistor T4 includes the initialization channel 131d, an initialization gate electrode 155d, an initialization source electrode 136d, and an initialization drain electrode 137d. Two initialization gate electrodes 155d (e.g., part of the previous-stage scan line 152) may prevent a leakage current and overlap the initialization channel 131d. The initialization source electrode 136d and the initialization drain electrode 137d are disposed on respective nearby sides of the initialization channel 131d. The initialization source electrode 136d is connected to the second data connecting member 175 through a contact hole 64.

[0085] The operation control transistor T5 includes the operation control channel 131e, an operation control gate electrode 155e, an operation control source electrode 136e, and an operation control drain electrode 137e. The operation control gate electrode 155e that is part of the light emission control line 153 overlaps the operation control channel 131e. The operation control source electrode 136e and the operation control drain electrode 137e are disposed on respective nearby sides of the operation control channel 131e. The operation control source electrode 136e is connected to a part extending from the driving voltage line 172 through a contact hole 65.

[0086] The light emission control transistor T6 includes the light emission control channel 131f, a light emission control gate electrode 155f, a light emission control source electrode 136f, and a light emission control drain electrode 137f. The light emission control gate electrode 155f which is part of the light emission control line 153 overlaps the light emission control channel 131f. The light emission control source electrode 136f and the light emission control drain electrode 137f are formed on respective nearby sides of the light emission control channel 131f. The light emission control drain electrode 137f is connected to a third data connecting member 179 through a contact hole 66.

[0087] The driving channel 131a of the driving transistor T1 includes a first end connected to the switching drain electrode 137b and the operation control drain electrode 137e, and a second end connected to the compensation source electrode 136c and the light emission control source electrode 136f.

[0088] The storage capacitor Cst includes the first storage electrode 155a and a second storage electrode 156 disposed with the second gate insulating layer 142 therebetween. The first storage electrode 155a corresponds to the driving gate electrode 155a. The second storage electrode 156 extends from the storage line 157, is larger than the driving gate electrode 155a, and covers the en-

tire driving gate electrode 155a.

[0089] Here, the second gate insulating layer 142 becomes a dielectric material, and storage capacitance is determined by a voltage between the charges stored in the storage capacitor Cst and the capacitive plates 155a and 156. By using the driving gate electrode 155a as a first storage electrode 155a, a space for providing a storage capacitor may be acquired in the space that is narrowed by the driving channel 131a occupying a large area in the pixel.

[0090] The first storage electrode 155a that is the driving gate electrode 155a is connected to a first end of the first data connecting member 174 through the contact hole 61 and a storage opening 51. The storage opening 51 is an opening formed in the second storage electrode 156. Therefore, the contact hole 61 connecting the first end of the first data connecting member 174 and the driving gate electrode 155a is disposed in the storage opening 51. The first data connecting member 174 is disposed on a same layer as the data line 171 and extends in a direction substantially parallel to the direction in which the data line 171 extends. A second end of the first data connecting member 174 is connected to the compensation drain electrode 137c of the compensation transistor T3 and the initialization drain electrode 137d of the initialization transistor T4 through the contact hole 63. Therefore, the first data connecting member 174 connects the driving gate electrode 155a, the compensation drain electrode 137c of the compensation transistor T3, and the initialization drain electrode 137d of the initialization transistor T4.

[0091] Therefore, the storage capacitor Cst stores a storage capacitance corresponding to a difference between the driving voltage (ELVDD) transmitted to the second storage electrode 156 through the driving voltage line 172 and the driving gate voltage (Vg) of the driving gate electrode 155a.

[0092] The third data connecting member 179 is connected to the pixel electrode 191 through a contact hole 81. The second data connecting member 175 is connected to the initialization voltage line 192 through a contact hole 82.

[0093] A cross-sectional configuration of an organic light emitting device according to an embodiment of the invention will now be described with respect to a stacking order.

[0094] The buffer layer 120 is formed on the substrate 110.

[0095] The semiconductor 130 including a channel 131, which includes the driving channel 131a, the switching channel 131b, the compensation channel 131c, the initialization channel 131d, the operation control channel 131e, and the light emission control channel 131f, is formed on the buffer layer 120. The driving source electrode 136a and the driving drain electrode 137a are disposed on respective sides of the driving channel 131a of the semiconductor 130. A switching source electrode 136b and a switching drain electrode 137b are disposed

on respective sides of the switching channel 131b. The compensation source electrode 136c and the compensation drain electrode 137c are disposed on respective sides of the compensation channel 131c. The initialization source electrode 136d and the initialization drain electrode 137d are disposed on respective sides of the initialization channel 131d. The operation control source electrode 136e and the operation control drain electrode 137e are disposed on respective sides of the operation control channel 131e. The light emission control source electrode 136f and the light emission control drain electrode 137f are disposed on respective sides of the light emission control channel 131f.

[0096] The first gate insulating layer 141, which covers the semiconductor 130, is formed on the semiconductor 130. First gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f, which include the scan line 151 including the switching gate electrode 155b and the compensation gate electrode 155c, the previous-stage scan line 152 including the initialization gate electrode 155d, the light emission control line 153 including the operation control gate electrode 155e and the light emission control gate electrode 155f, and the driving gate electrode (e.g., a first storage electrode) 155a are formed on the first gate insulating layer 141.

[0097] The second gate insulating layer 142, which covers the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f and the first gate insulating layer 141, is formed on the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f and the first gate insulating layer 141.

[0098] Second gate wires 157 and 156, which include the storage line 157 disposed substantially parallel to the scan line 151 and the second storage electrode 156 which is a portion extending from the storage line 157, are formed on the second gate insulating layer 142. The first dummy metal layer 510 disposed in the non-display area (NA) may be made of a same material as the second gate wires 157 and 156 disposed in the display area (DA). In addition, the first dummy metal layer 510 may be disposed in a same layer as the second gate wires 157 and 156. The second gate wires 157 and 156 and the first dummy metal layer 510 may be substantially simultaneously formed by depositing a metal material on the second gate insulating layer 142 and patterning the same.

[0099] The interlayer insulating layer 160 is formed on the second gate insulating layer 142 and the second gate wires 157 and 156.

[0100] Contact holes 61, 62, 63, 64, 65, and 66, which expose at least part of an upper side of the semiconductor 130, are formed in the interlayer insulating layer 160.

[0101] Data wires 171, 172, 174, 175, and 179, which include the data line 171, the driving voltage line 172, the first data connecting member 174, the second data connecting member 175, and the third data connecting member 179, are formed on the interlayer insulating layer 160. The second dummy metal layer 520 disposed in the non-display area (NA) may be made of a same material as

the data wires 171, 172, 174, 175, and 179 disposed in the display area (DA). Further, the second dummy metal layer 520 may be disposed in a same layer as the data wires 171, 172, 174, 175, and 179. The data wires 171, 172, 174, 175, and 179 and the second dummy metal layer 520 may be substantially simultaneously formed by depositing a metal material on the interlayer insulating layer 160 and patterning the same.

[0102] The data line 171 is connected to the switching source electrode 136b through the contact hole 62. The first data connecting member 174 includes a first end connected to the first storage electrode 155a through the contact hole 61, and a second end connected to the compensation drain electrode 137c and the initialization drain electrode 137d through the contact hole 63. The second data connecting member 175, which extends in a direction substantially parallel to that of the data line 171, is connected to the initialization source electrode 136d through the contact hole 64. The third data connecting member 179 is connected to the light emission control drain electrode 137f through the contact hole 66.

[0103] A passivation layer 180 covering the data wires 171, 172, 174, 175, and 179 and the interlayer insulating layer 160 is formed on the data wires 171, 172, 174, 175, and 179 and the interlayer insulating layer 160.

[0104] The pixel electrode 191 and the initialization voltage line 192 are formed on the passivation layer 180. The third data connecting member 179 is connected to the pixel electrode 191 through the contact hole 81 formed in the passivation layer 180, and the second data connecting member 175 is connected to the initialization voltage line 192 through the contact hole 82 formed in the passivation layer 180.

[0105] A pixel defined layer (PDL) 350 that covers the passivation layer 180, the initialization voltage line 192, and the pixel electrode 191 is formed on the passivation layer 180, the initialization voltage line 192, and the pixel electrode 191. For example, the pixel defined layer 350 may be formed on edges of the passivation layer 180, the initialization voltage line 192, and the pixel electrode 191. The pixel defined layer 350 includes a pixel opening 351 that exposes the pixel electrode 191.

[0106] The organic emission layer 370 is disposed on the pixel electrode 191 exposed by the pixel opening 351, and the common electrode 270 is disposed on the organic emission layer 370. The common electrode 270 is formed on the pixel defined layer 350 and is formed throughout a plurality of pixels PX. In this way, the organic light emitting diode (OLED) including the pixel electrode 191, the organic emission layer 370, and the common electrode 270 is formed.

[0107] According to an embodiment of the present invention, a method of manufacturing an organic light emitting device includes disposing the first dummy metal layer 510 on the first substrate 110 in the non-display area (NA), disposing the interlayer insulating layer 160 on the first dummy metal layer 510, and forming the first contact hole 161 in the interlayer insulating layer 160. The first

contact hole 161 overlaps a portion of the first dummy metal layer 510. The method further includes disposing the second dummy metal layer 520 on the interlayer insulating layer 160 and within the first contact hole 161.

5 The second dummy metal layer 520 overlaps the first dummy metal layer 510 and is electrically connected to the first dummy metal layer 510 through the first contact hole 161. The method further includes attaching the second substrate 210 to the first substrate 110 using the sealant 650. The sealant 650 is disposed between the first substrate 110 and the second substrate 210, and the sealant 650 overlaps and contacts the second dummy metal layer 520.

[0108] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIG. 9.

[0109] The organic light emitting device according to the embodiment of the invention shown in FIG. 9 includes similar elements and configurations as those described with reference to the organic light emitting device according to the embodiment shown in FIGS. 1 to FIG. 8. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. In the exemplary embodiment described with reference to FIG. 9, a formation position of the first dummy metal layer is different from the embodiment previously described. An embodiment of the invention according to FIG. 9 will now be described.

[0110] FIG. 9 shows a cross-sectional view of an organic light emitting device according to an embodiment of the invention. FIG. 9 shows the portion A that is in the non-display area (NA) of FIG. 1, similar to FIG. 3.

[0111] In the embodiment previously described, the first dummy metal layer 510 is disposed above the second gate insulating layer 142. In the embodiment shown in FIG. 9, the first dummy metal layer 510 is disposed below the second gate insulating layer 142. The first dummy metal layer 510 is disposed between the first gate insulating layer 141 and the second gate insulating layer 142.

[0112] The first dummy metal layer 510 provided in the non-display area (NA) may be made of a same material as the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f of FIGS. 5 to 8 disposed in the display area (DA). The first dummy metal layer 510 may be disposed in a same layer as the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f. The first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f of FIGS. 5 to 8 and the first dummy metal layer 510 may be substantially simultaneously formed by depositing a metal material on the first gate insulating layer 141 and patterning the same.

[0113] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIG. 10.

[0114] The organic light emitting device according to the embodiment shown in FIG. 10 includes similar elements and configurations as those described with refer-

ence to the organic light emitting device according to the embodiment shown in FIGs. 1 to 8. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. In the embodiment described with reference to FIG. 9, a shape of an edge of the second dummy metal layer is different from that of the embodiment previously described. An embodiment according to FIG. 10 will now be described.

[0115] FIG. 10 shows a top plan view of an organic light emitting device according to an exemplary embodiment. FIG. 10 shows the portion A that is in the non-display area (NA) of FIG. 1, similar to FIG. 2.

[0116] As shown in FIG. 10, the organic light emitting device includes the first substrate 110, the dummy metal layer 500 disposed on the first substrate 110, the second substrate 210 that covers the first substrate 110, and the sealant 650 that bonds the first substrate 110 and the second substrate 210, similar to the previous embodiment.

[0117] The dummy metal layer 500 includes the first dummy metal layer 510 and the second dummy metal layer 520. In the exemplary embodiment previously described, the second dummy metal layer 520 has a bar shape extending substantially parallel to the edge of the first substrate 110, and an edge of the second dummy metal layer 520 has a linear shape (e.g., the edge of the second dummy metal layer 520 extends in a substantially straight line) (see FIG. 2). In the embodiment of FIG. 10, the second dummy metal layer 520 has a bar shape extending substantially parallel to the edge of the first substrate 110 (e.g., the second dummy metal layer 520 extends lengthwise in a direction substantially parallel to the edge of the first substrate 110), and an edge of the second dummy metal layer 520 has a shape that includes a plurality of protrusions and depressions. For example, as shown in FIG. 10, protrusions and depressions may be alternately included at the edge of the second dummy metal layer 520. Thus, in an embodiment of the invention, the second dummy metal layer 520 has a bar shape extending in a first direction substantially parallel to the edge of the first substrate 110, and a plurality of protrusions and depressions extending in a second direction crossing the first direction (e.g., substantially perpendicular to the first direction).

[0118] A first edge of the second dummy metal layer 520 disposed near the edge of the first substrate 110 and a second edge of the second dummy metal layer 520 disposed on the opposite side of the first edge have shapes that include protrusions and depressions, as shown in FIG. 10. That is, respective edges of the second dummy metal layer 520 substantially parallel to the edge of the first substrate 110 have shapes that include protrusions and depressions. As a result, a total length of the edge of the second dummy metal layer 520 is longer than the total length of the edge of the second dummy metal layer of the previous embodiment. Therefore, when a permeation path of external oxygen or moisture in-

creases, the permeation may be efficiently prevented or reduced, and static electricity may be efficiently dispersed.

[0119] It has been described above that in an embodiment, the respective edges of the second dummy metal layer 520 have a shape that includes protrusions and depressions. However, the present invention is not limited thereto. For example, in an embodiment, one edge of the second dummy metal layer 520 may have a shape that includes protrusions and depressions, and the edge on the opposite side may have a linear shape (e.g., the edge may extend in a substantially straight line without any protrusions and depressions).

[0120] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIGs. 11 and 12.

[0121] The organic light emitting device according to the embodiment shown in FIGs. 11 and 12 includes similar elements and configurations as those described with reference to the organic light emitting device according to the embodiment shown in FIGs. 1 to 8. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. The embodiment shown in FIGs. 11 and 12 is different from the previous embodiment in that a hole pattern is generated in the first dummy metal layer, which will now be described.

[0122] FIG. 11 shows a top plan view of an organic light emitting device according to an embodiment of the invention. FIG. 12 shows a cross-sectional view of an organic light emitting device according to an embodiment with respect to line XII-XII of FIG. 11. FIGs. 11 and 12 show portion A that is in the non-display area (NA) of FIG. 1 according to an embodiment.

[0123] As shown in FIGs. 11 and 12, the organic light emitting device includes the first substrate 110, the dummy metal layer 500 disposed on the first substrate 110, the second substrate 210 that covers the first substrate 110, and the sealant 650 that bonds the first substrate 110 and the second substrate 210, which is similar to the previous exemplary embodiment.

[0124] The dummy metal layer 500 includes the first dummy metal layer 510 and the second dummy metal layer 520. In the embodiment previously described, the first dummy metal layer 510 has a bar shape extending substantially parallel to the edge of the first substrate 110, and no additional pattern is provided inside the bar shape. In the exemplary embodiment shown in FIGs. 11 and 12, the first dummy metal layer 510 has a bar shape substantially extending in parallel to the edge of the first substrate 110, and a hole pattern 512 is formed in the first dummy metal layer 510. The hole pattern 512 may be substantially simultaneously formed during a process of forming the first dummy metal layer 510 by depositing a metal material on the gate insulating layer 140 and patterning the same. Although the hole pattern 512 is shown as having a substantially quadrangle shape, the present invention is not limited thereto. For example, in

exemplary embodiments, the hole pattern 512 may be variously modified to form a plurality of different shapes.

[0125] The hole pattern 512 is formed at a position where the first dummy metal layer 510 does not overlap the second dummy metal layer 520. Therefore, the hole pattern 512 does not overlap the second dummy metal layer 520.

[0126] The interlayer insulating layer 160 is disposed between the first dummy metal layer 510 and the second dummy metal layer 520, which overlap each other. The first contact hole 161 overlaps at least part of the first dummy metal layer 510 and is generated in the interlayer insulating layer 160. The second contact hole 162 is further formed in the interlayer insulating layer 160. The second contact hole 162 is disposed in the hole pattern 512. The second contact hole 162 may be disposed in a matrix form in the horizontal direction and the vertical direction in a plan view. For example, in an embodiment, sixteen second contact holes 162 disposed in a 4x4 matrix form may configure one set, and one set of second contact holes 162 may be disposed in one hole pattern 512. A plurality of hole patterns 512 may be disposed in a matrix form. Therefore, sets of the second contact holes 162 may be disposed in a matrix form. The above-described disposals of the second contact holes 162 and the hole patterns 512 are, and are modifiable in various ways.

[0127] The second contact hole 162 is formed in the gate insulating layer 140 and the buffer layer 120 disposed below the interlayer insulating layer 160. Therefore, the sealant 650 may contact the first substrate 110 through the second contact hole 162. However, the present invention is not limited thereto. For example, in an embodiment, the second contact hole 162 may be formed in the interlayer insulating layer 160. Further, the second contact hole 162 may be formed in the interlayer insulating layer 160 and the gate insulating layer 140 disposed below the same.

[0128] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIG. 13.

[0129] The organic light emitting device according to the embodiment shown in FIG. 13 includes similar elements and configurations as those described with reference to the organic light emitting device according to the embodiment shown in FIGs. 11 and 12. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. In the embodiment described with reference to FIG. 13, a formation position of the first dummy metal layer is different from the embodiment previously described. An embodiment of the invention according to FIG. 13 will now be described.

[0130] FIG. 13 shows a cross-sectional view of an organic light emitting device according to an embodiment of the invention. FIG. 13 shows portion A that is in the non-display area (NA) of FIG. 1, similar to FIG. 12.

[0131] In the embodiment previously described, the

first dummy metal layer 510 is disposed over the second gate insulating layer 142. In the embodiment shown in FIG. 13, the first dummy metal layer 510 may be disposed below the second gate insulating layer 142. The first dummy metal layer 510 may be disposed between the first gate insulating layer 141 and the second gate insulating layer 142.

[0132] The first dummy metal layer 510 disposed in the non-display area (NA) may be made of a same material as the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f of FIGs. 5 to 8 disposed in the display area (DA), and may be disposed in a same layer as the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f. The first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f of FIGs. 5 to 8 and the first dummy metal layer 510 may be substantially simultaneously formed by depositing a metal material on the first gate insulating layer 141 and patterning the same.

[0133] An organic light emitting device according to an embodiment will now be described with reference to FIG. 14.

[0134] The organic light emitting device according to the embodiment shown in FIG. 14 includes similar elements and configurations as those described with reference to the organic light emitting device according to the exemplary embodiment shown in FIGs. 11 and 12. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. In the embodiment described with reference to FIG. 14, a shape of an edge of the second dummy metal layer is different from the embodiment previously described. An embodiment according to FIG. 14 will now be described.

[0135] FIG. 14 shows a top plan view of an organic light emitting device according to an embodiment of the invention. FIG. 14 shows portion A that is in the non-display area (NA) of FIG. 1.

[0136] As shown in FIG. 14, the organic light emitting device includes the first substrate 110, the dummy metal layer 500 disposed on the first substrate 110, the second substrate 210 that covers the first substrate 110, and the sealant 650 that bonds the first substrate 110 and the second substrate 210, which is similar to the embodiment previously described. The first contact hole 161 and the second contact hole 162 are formed in the interlayer insulating layer 160, which is disposed between the first dummy metal layer 510 and the second dummy metal layer 520. The second contact hole 162 is disposed in the hole pattern 512 of the first dummy metal layer 510, which is similar to the embodiment previously described.

[0137] In the embodiment previously described, the second dummy metal layer 520 has a bar shape extending substantially parallel to the edge of the first substrate 110, and the edge of the second dummy metal layer 520 has a linear shape (e.g., the edge of the second dummy metal layer 520 extends in a substantially straight line). In the embodiment shown in FIG. 14, the second dummy

metal layer 520 has a bar shape extending substantially parallel to the edge of the first substrate 110 (e.g., the second dummy metal layer 520 extends lengthwise in a direction substantially parallel to the edge of the first substrate 110), and the edge of the second dummy metal layer 520 has a shape that includes a plurality of protrusions and depressions. For example, as shown in FIG. 14, protrusions and depressions may be alternately included at the edge of the second dummy metal layer 520. Thus, in an embodiment, the second dummy metal layer 520 has a bar shape extending in a first direction substantially parallel to the edge of the first substrate 110, and a plurality of protrusions and depressions extending in a second direction crossing the first direction (e.g., substantially perpendicular to the first direction).

[0138] A first edge of the second dummy metal layer 520 disposed near the edge of the first substrate 110 and a second edge disposed opposite the first edge have shapes including protrusions and depressions. That is, respective edges of the second dummy metal layer 520 that are substantially parallel to the edge of the first substrate 110 have shapes including protrusions and depressions. As a result, the edge of the second dummy metal layer 520 is longer than the edge of the second dummy metal layer of the embodiment previously described. Therefore, when a permeation path of external oxygen or moisture increases, the permeation may be efficiently prevented or reduced, and static electricity may be efficiently dispersed.

[0139] It has been described that the respective edges of the second dummy metal layer 520 have a shape including protrusions and depressions. However, the present invention is not limited thereto. For example, in an embodiment of the invention, one edge of the second dummy metal layer 520 may have a shape including protrusions and depressions and the edge on the opposite side may have a linear shape.

[0140] An organic light emitting device according to an embodiment will now be described with reference to FIGs. 15 and 16.

[0141] The organic light emitting device according to the embodiment shown in FIGs. 15 and 16 includes similar elements and configurations as those described with reference to the organic light emitting device according to the embodiment shown in FIGs. 1 to 8. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. The embodiment described with reference to FIGs. 15 and 16 is different from the embodiment previously described in that a third contact hole is further formed in the interlayer insulating layer.

[0142] FIG. 15 shows a top plan view of an organic light emitting device according to an embodiment of the invention. FIG. 16 shows a cross-sectional view of an organic light emitting device according to an embodiment with respect to line XVI-XVI of FIG. 15. FIGs. 15 and 16 show portion A that is in the non-display area (NA) of FIG. 1.

[0143] As shown in FIGs. 15 and 16, the organic light emitting device includes the first substrate 110, the dummy metal layer 500 disposed on the first substrate 110, the second substrate 210 that covers the first substrate 110, and the sealant 650 that bonds the first substrate 110 and the second substrate 210, which is similar to the embodiment previously described.

[0144] The dummy metal layer 500 includes the first dummy metal layer 510 and the second dummy metal layer 520. The interlayer insulating layer 160 is disposed on the first dummy metal layer 510. The first contact hole 161 and a third contact hole 163 overlapping at least part of the first dummy metal layer 510 are formed in the interlayer insulating layer 160. The first contact hole 161 is disposed at a portion where the first dummy metal layer 510 overlaps the second dummy metal layer 520. The first dummy metal layer 510 is connected to the second dummy metal layer 520 through the first contact hole 161. The third contact hole 163 is disposed at a portion where the first dummy metal layer 510 does not overlap the second dummy metal layer 520. The first dummy metal layer 510 contacts the sealant 650 through the second contact hole 162.

[0145] Similar to the first contact hole 161, the third contact hole 163 may be disposed in a matrix form in the horizontal direction and the vertical direction on the plane. For example, in an embodiment, sixteen third contact holes 163 disposed in a 4x4 matrix form may configure one set. A plurality of sets of the third contact holes 163 may be disposed in a matrix form. However, the present invention is not limited thereto.

[0146] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIG. 17.

[0147] The organic light emitting device according to the embodiment of the invention shown in FIG. 17 includes similar elements and configurations as those described with reference to the organic light emitting device according to the exemplary embodiment shown in FIGs. 15 and 16. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. In the embodiment of the invention described with reference to FIG. 17, a formation position of the first dummy metal layer is different from the embodiment previously described. An embodiment of the invention according to FIG. 17 will now be described.

[0148] FIG. 17 shows a cross-sectional view of an organic light emitting device according to an embodiment of the invention. FIG. 17 shows portion A that is in the non-display area (NA) of FIG. 1 similar to FIG. 16.

[0149] In the exemplary embodiment previously described, the first dummy metal layer 510 is disposed over the second gate insulating layer 142. In the embodiment shown in FIG. 17, the first dummy metal layer 510 may be disposed below the second gate insulating layer 142. Further, the first dummy metal layer 510 may be disposed between the first gate insulating layer 141 and the second

gate insulating layer 142.

[0150] The first dummy metal layer 510 disposed in the non-display area (NA) may be made of a same material as the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f of FIGs. 5 to 8 disposed in the display area (DA), and may be disposed in a same layer as the first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f. The first gate wires 151, 152, 153, 155a, 155b, 155c, 155d, 155e, and 155f of FIGs. 5 to 8 and the first dummy metal layer 510 may be substantially simultaneously formed by depositing a metal material on the first gate insulating layer 141 and patterning the same.

[0151] An organic light emitting device according to an embodiment of the invention will now be described with reference to FIG. 18.

[0152] The organic light emitting device according to the embodiment shown in FIG. 18 includes similar elements and configurations as those described with reference to the organic light emitting device according to the embodiment shown in FIGs. 15 and 16. For convenience of explanation, a further description of elements and configurations previously described may be omitted herein. In the embodiment described with reference to FIG. 18, a shape of an edge of the second dummy metal layer is different from the exemplary embodiment previously described. An embodiment of the invention according to FIG. 18 will now be described.

[0153] FIG. 18 shows a top plan view of an organic light emitting device according to an embodiment. FIG. 18 shows portion A that is in the non-display area (NA) of FIG. 1 similar to FIG. 15.

[0154] As shown in FIG. 18, the organic light emitting device includes the first substrate 110, the dummy metal layer 500 disposed on the first substrate 110, the second substrate 210 that covers the first substrate 110, and the sealant 650 that bonds the first substrate 110 and the second substrate 210, which is similar to the embodiment previously described.

[0155] The dummy metal layer 500 includes the first dummy metal layer 510 and the second dummy metal layer 520. In the embodiment previously described, the second dummy metal layer 520 has a bar shape extending substantially parallel to the edge of the first substrate 110, and an edge of the second dummy metal layer 520 has a linear shape. In the embodiment shown in FIG. 18, the second dummy metal layer 520 has a bar shape extending substantially parallel to the edge of the first substrate 110 (e.g., the second dummy metal layer 520 extends lengthwise in a direction substantially parallel to the edge of the first substrate 110), and an edge of the second dummy metal layer 520 has a shape including protrusions and depressions. For example, as shown in FIG. 18, protrusions and depressions may be alternately included at the edge of the second dummy metal layer 520. Thus, in an embodiment, the second dummy metal layer 520 has a bar shape extending in a first direction substantially parallel to the edge of the first substrate

110, and a plurality of protrusions and depressions extending in a second direction crossing the first direction (e.g., substantially perpendicular to the first direction).

[0156] A first edge of the second dummy metal layer 520 disposed near the edge of the first substrate 110 and a second edge of the second dummy metal layer 520 disposed on the opposite side of the first edge have shapes including protrusions and depressions. That is, respective edges of the second dummy metal layer 520 substantially parallel to the edge of the first substrate 110 have shapes including protrusions and depressions. As a result, the edge of the second dummy metal layer 520 is longer than the edge of the second dummy metal layer of the embodiment previously described. Therefore, when a permeation path of external oxygen or moisture increases, the permeation may be efficiently prevented or reduced, and static electricity may be efficiently dispersed.

[0157] Although it has been described herein that the respective edges of the second dummy metal layer 520 have a shape including protrusions and depressions, the present invention is not limited thereto. For example, in an embodiment of the invention, one edge of the second dummy metal layer 520 may have a shape including protrusions and depressions and the edge on the opposite side may have a linear shape.

[0158] Embodiments of the present invention provide an organic light emitting device in which a sealant is prevented from peeling off of a substrate.

[0159] According to embodiments of the present invention, the dummy metal layer includes a plurality of layers electrically connected to one another, thereby reducing resistance and preventing the sealant from being stripped off as a result of static electricity.

[0160] While the present invention has been particularly shown and described with reference to the exemplary embodiments thereof, it will be understood by those of ordinary skill in the art that various changes in form and detail may be made therein without departing from the scope of the present invention as defined by the following claims.

Claims

1. An organic light emitting device, comprising:

a first substrate comprising a display area and a non-display area;

a dummy metal layer disposed on the first substrate in the non-display area, wherein the dummy metal layer comprises a first dummy metal layer and a second dummy metal layer, and the first dummy metal layer and the second dummy metal layer overlap each other;

an insulating layer disposed between the first dummy metal layer and the second dummy metal layer in a cross-sectional view;

- a second substrate covering the first substrate;
and
a sealant disposed between the first substrate and the second substrate and overlapping the dummy metal layer,
wherein the first dummy metal layer is electrically connected to the second dummy metal layer, and the sealant contacts the second dummy metal layer.
2. An organic light emitting device according to claim 1, wherein
the insulating layer comprises a first contact hole overlapping at least a part of the first dummy metal layer, and
the second dummy metal layer is disposed on the insulating layer and is connected to the first dummy metal layer through the first contact hole.
3. An organic light emitting device according to claim 1 or 2, wherein a resistivity of the second dummy metal layer is less than a resistivity of the first dummy metal layer.
4. An organic light emitting device according to claim 3, wherein the first dummy metal layer is made of molybdenum, and the second dummy metal layer is made of aluminum.
5. An organic light emitting device according to any preceding claim, further comprising:

a semiconductor disposed on the first substrate in the display area;
a gate insulating layer disposed on the semiconductor;
a gate wire disposed on the gate insulating layer, wherein the insulating layer is disposed on the gate wire; and
a data wire disposed on the insulating layer.
6. An organic light emitting device according to claim 5, wherein the first dummy metal layer is made of a same material as the gate wire, and is disposed in a same layer as the gate wire.
7. An organic light emitting device according to claim 5 or 6, wherein the gate insulating layer comprises a first gate insulating layer and a second gate insulating layer, and
the gate wire comprises a first gate wire disposed between the first gate insulating layer and the second gate insulating layer in a cross-sectional view, and a second gate wire disposed on the second gate insulating layer.
8. An organic light emitting device according to claim 7, wherein the first dummy metal layer is made of a
- same material as the first gate wire or the second gate wire, and is disposed in a same layer as the first gate wire or the second gate wire.
9. An organic light emitting device according to any one of claims 6 to 8, wherein the second dummy metal layer is made of a same material as the data wire, and is disposed in a same layer as the data wire.
10. An organic light emitting device according to any preceding claim, wherein the first dummy metal layer and the second dummy metal layer have a bar shape extending substantially parallel to an edge of the first substrate.
11. An organic light emitting device, comprising:

a first substrate comprising a display area and a non-display area;
a second substrate opposing the first substrate;
a pixel disposed on the first substrate in the display area, wherein the pixel comprises:

a storage capacitor;
an organic light emitting diode comprising an anode and a cathode;
a driving transistor comprising a first gate electrode; and
a switching transistor comprising a second gate electrode;

a dummy metal layer disposed on the first substrate in the non-display area, wherein the dummy metal layer comprises a first dummy metal layer and a second dummy metal layer, and the first dummy metal layer and the second dummy metal layer overlap each other;
an insulating layer disposed on the first substrate in the non-display area between the first dummy metal layer and the second dummy metal layer in a cross-sectional view; and
a sealant disposed on the first substrate in the non-display area between the first substrate and the second substrate, and overlapping the dummy metal layer,
wherein the first dummy metal layer, the first gate electrode, and the second gate electrode are made of a same material.
12. An organic light emitting device according to claim 11, wherein the first gate electrode is connected to a first end of the storage capacitor, a second end of the storage capacitor is connected to a driving voltage line, the second gate electrode is connected to a scan line, the anode is connected to a drain electrode of the driving transistor, and the cathode is connected to a common voltage line.

13. An organic light emitting device according to claim 11 or 12, wherein the insulating layer comprises a first contact hole overlapping at least a part of the first dummy metal layer, and the second dummy metal layer is disposed on the insulating layer and is connected to the first dummy metal layer through the first contact hole. 5
14. An organic light emitting device according to claim 11, 12 or 13 wherein a resistivity of the second dummy metal layer is less than a resistivity of the first dummy metal layer. 10
15. An organic light emitting device according to claim 14, wherein the first dummy metal layer is made of molybdenum, and the second dummy metal layer is made of aluminum. 15

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FIG. 1

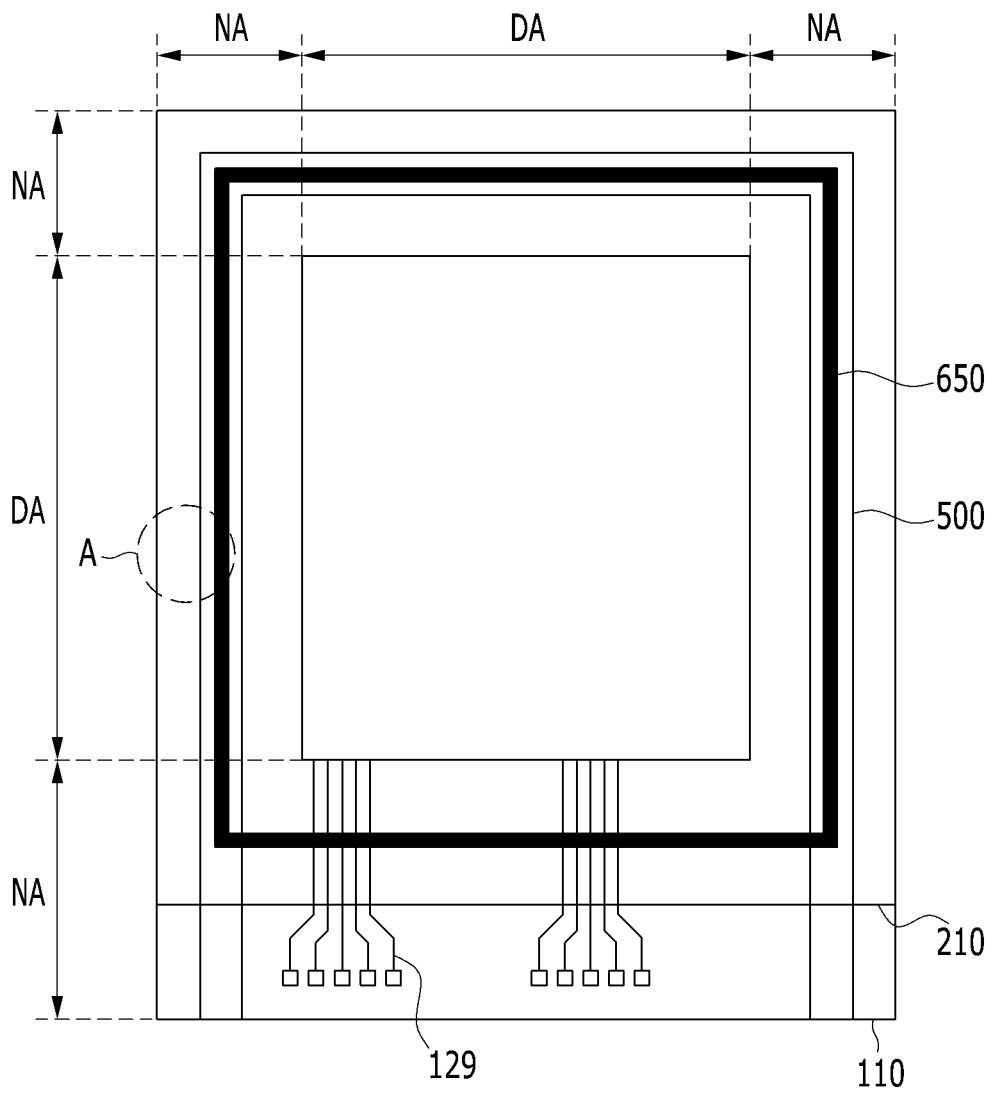


FIG. 2

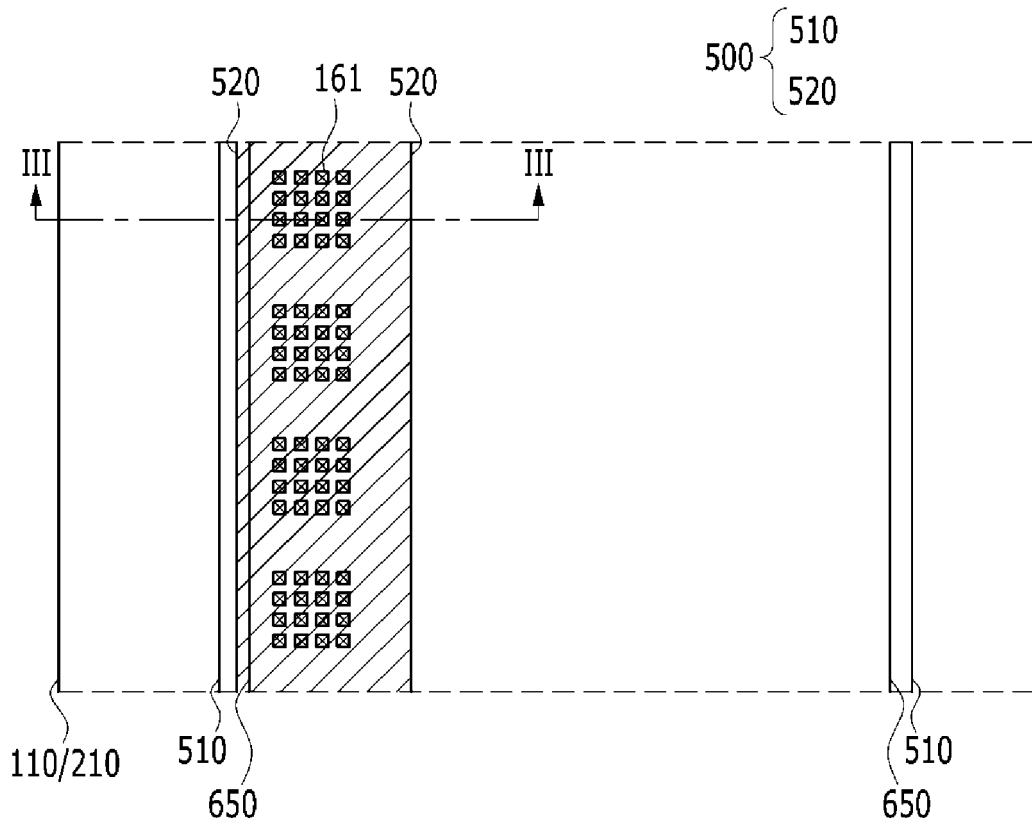


FIG. 3

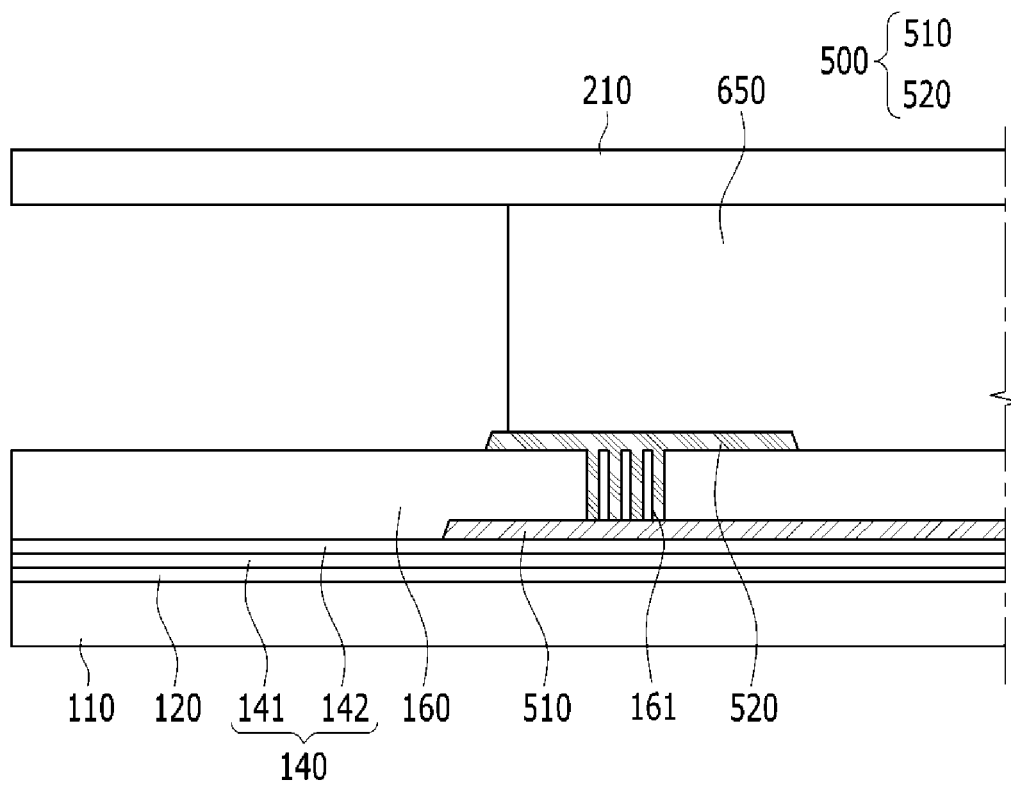


FIG. 5

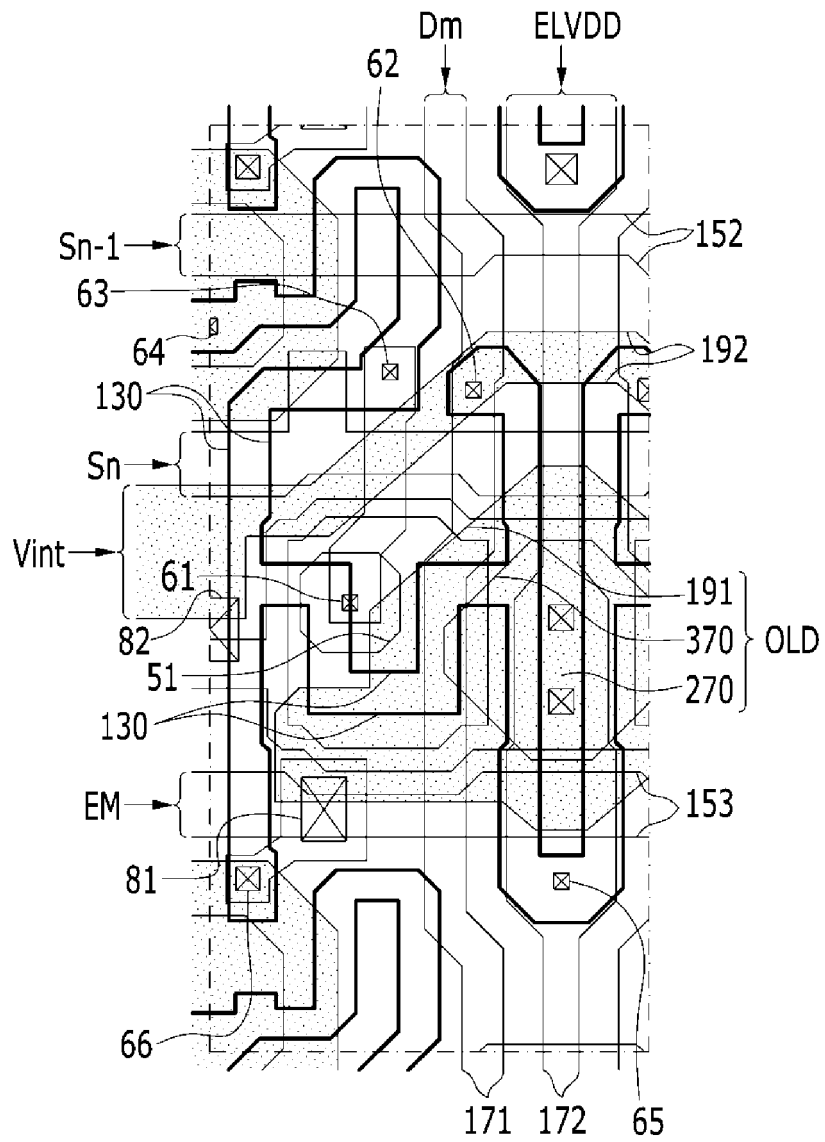


FIG. 6

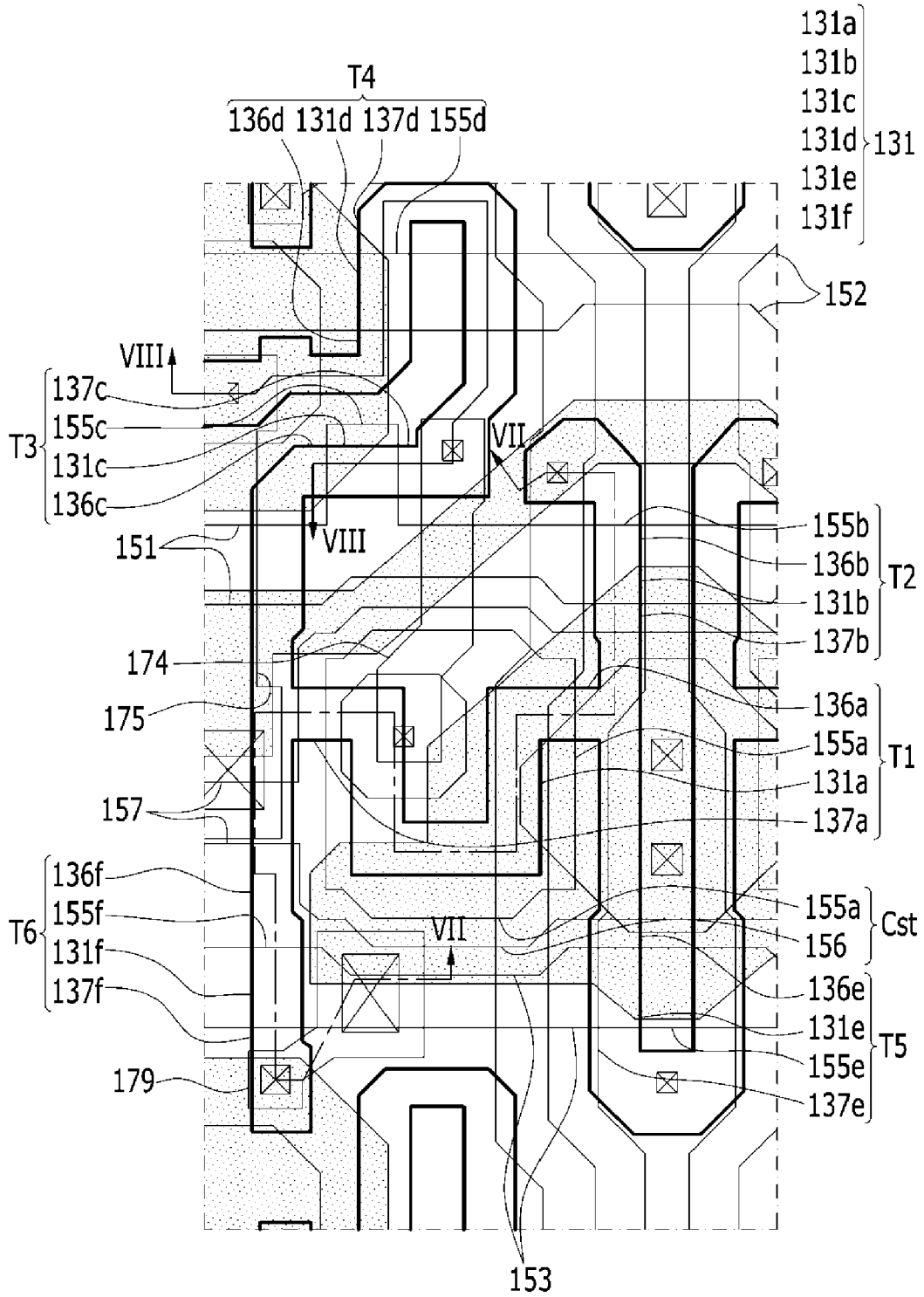


FIG. 7

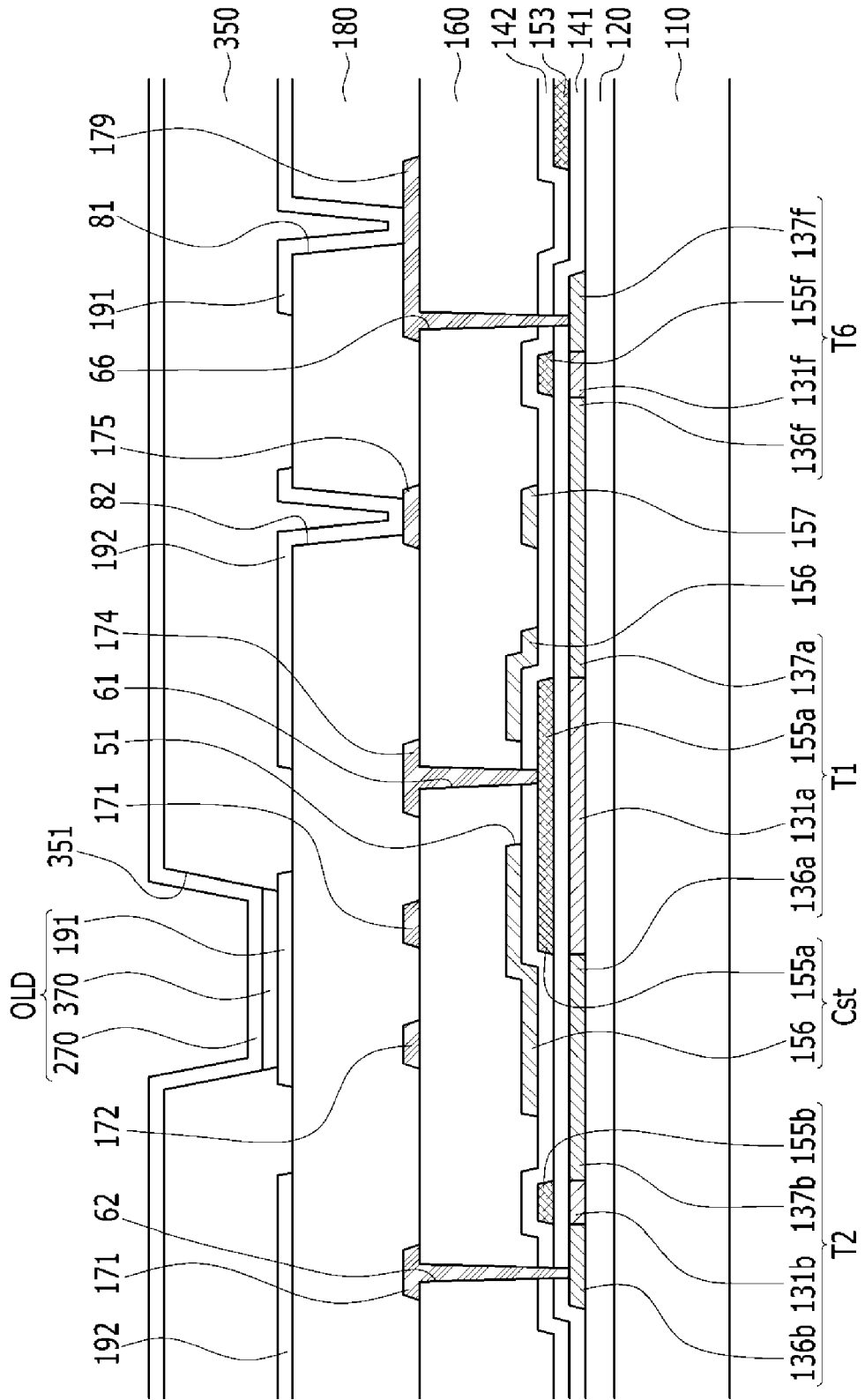


FIG. 8

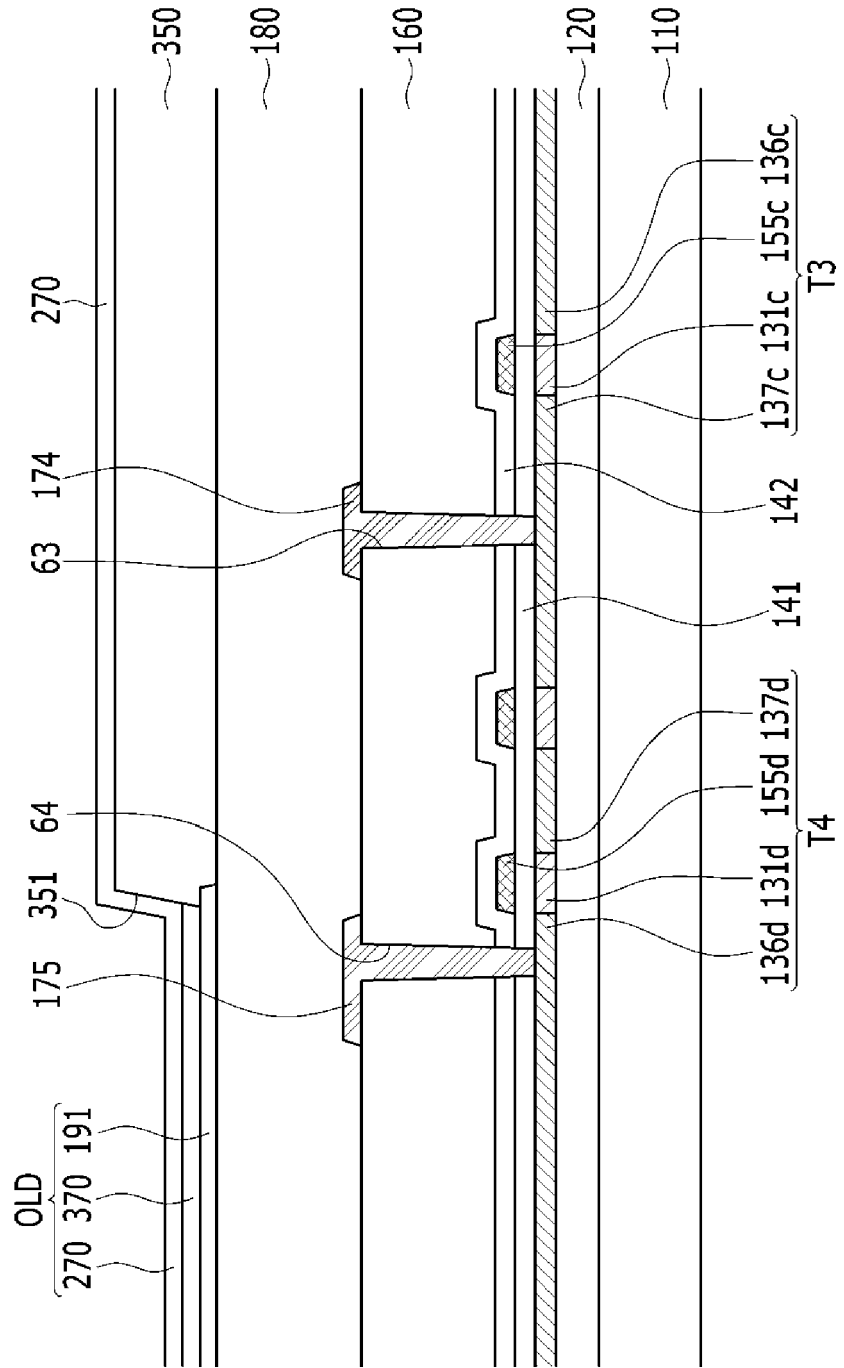


FIG. 9

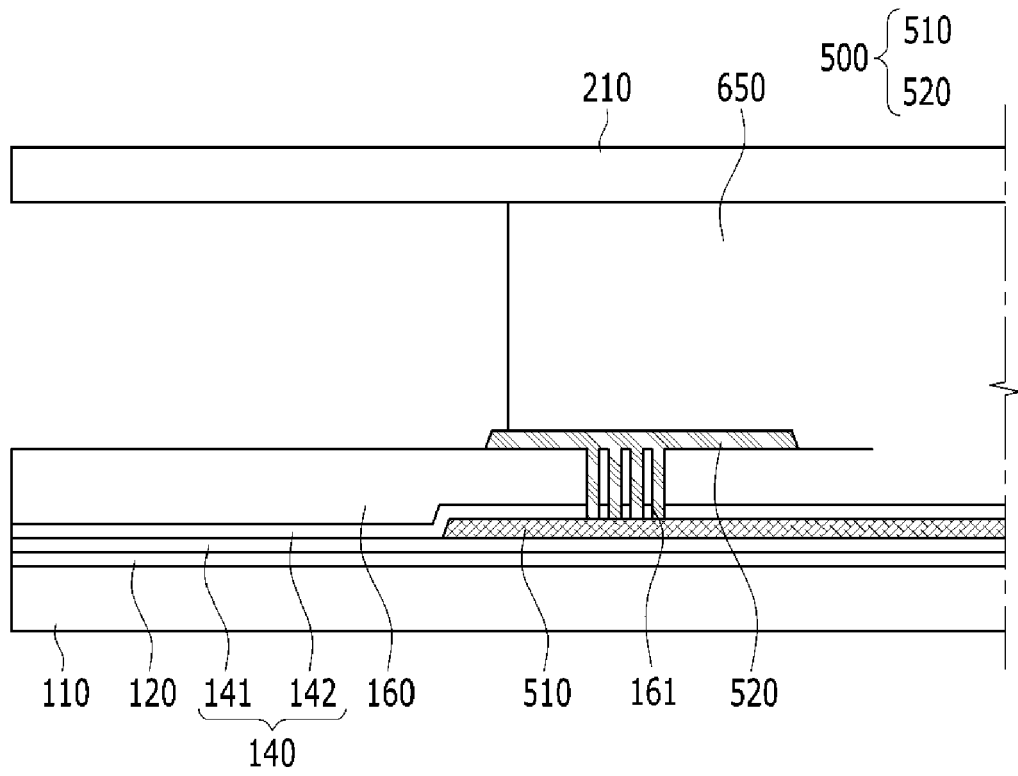


FIG. 10

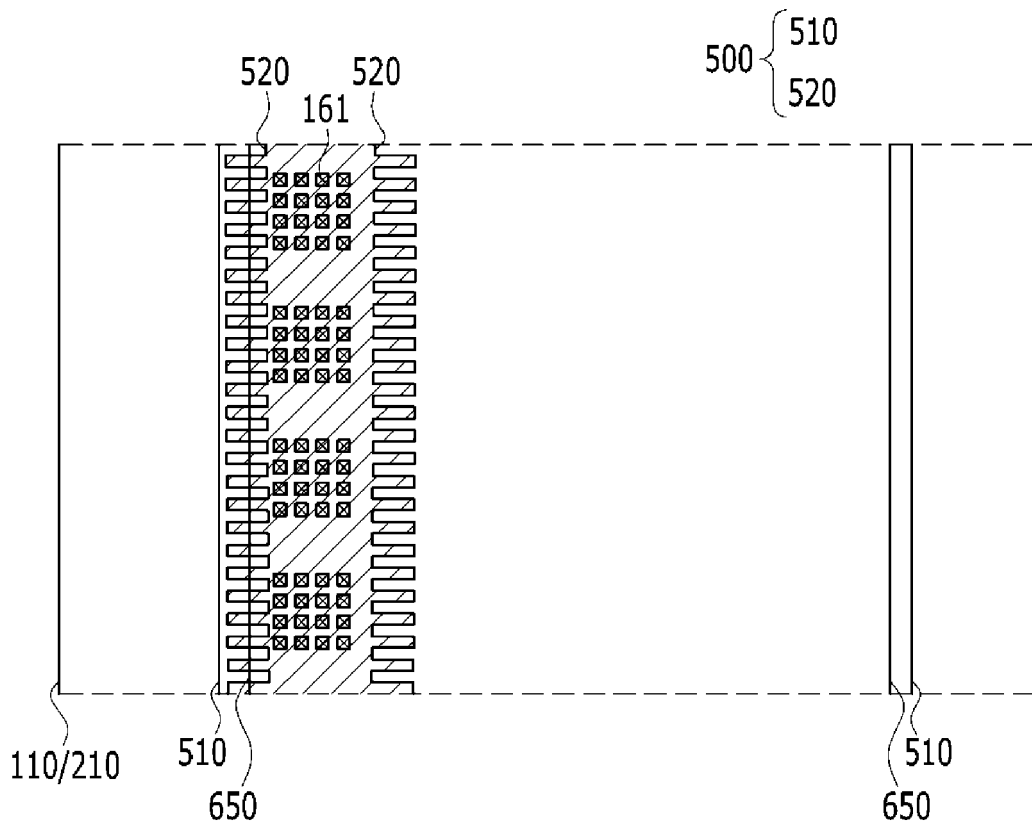


FIG. 11

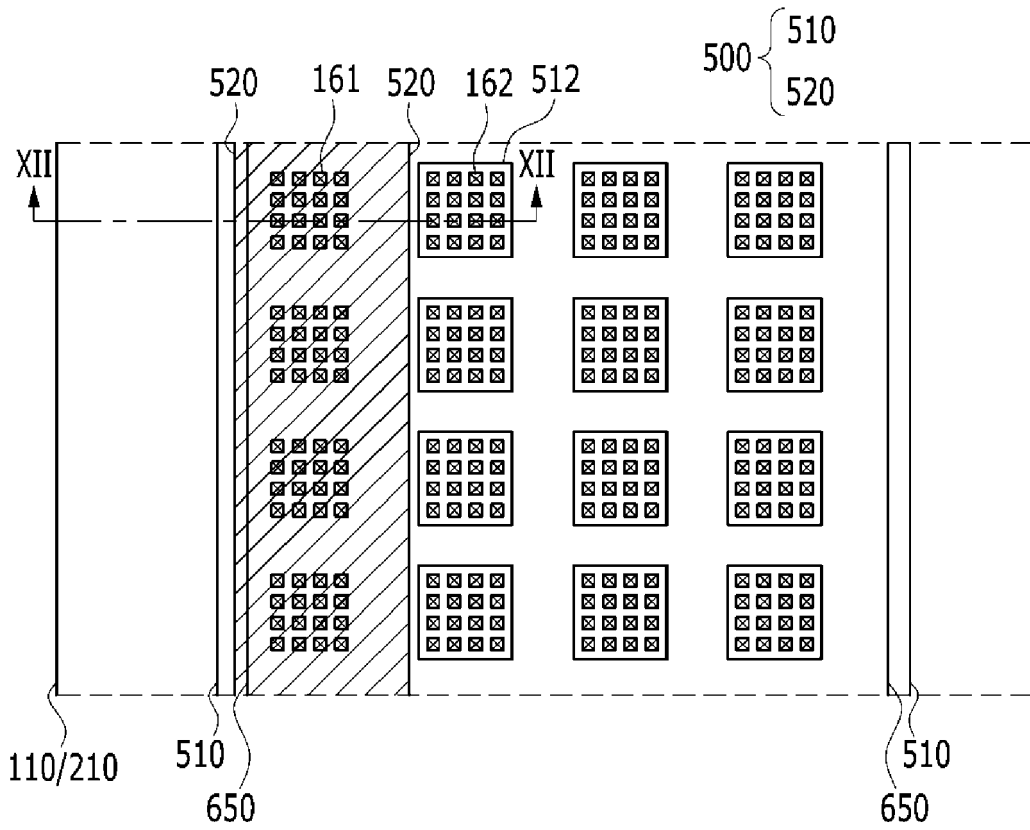


FIG. 12

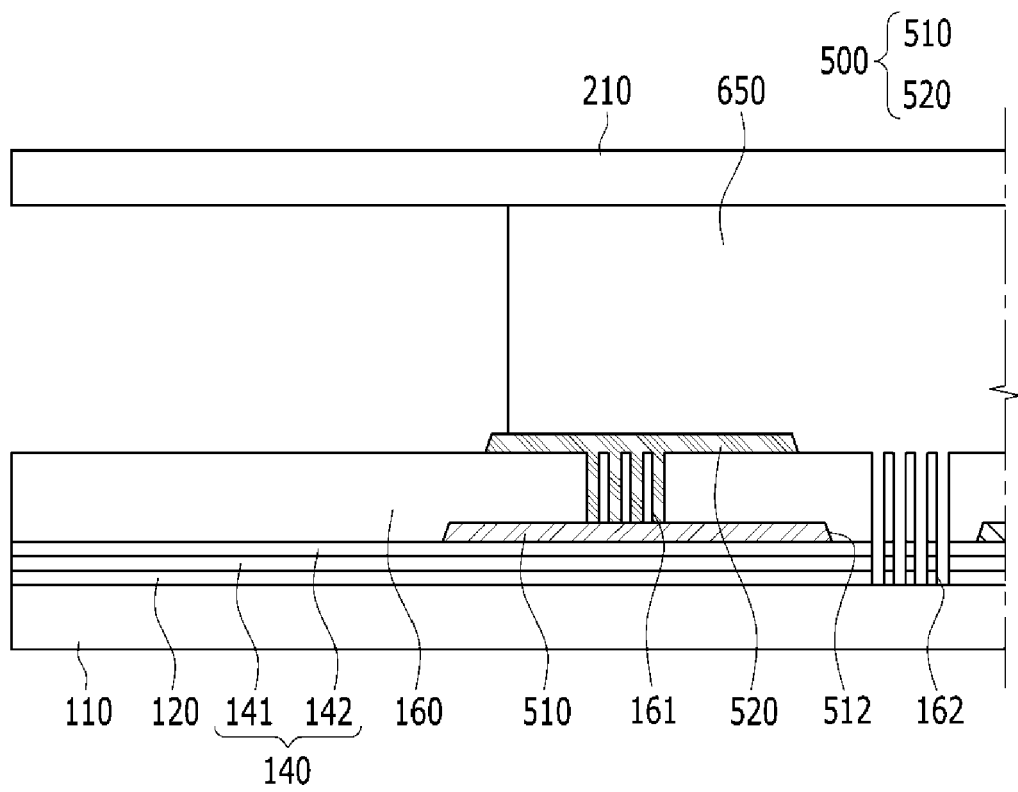


FIG. 13

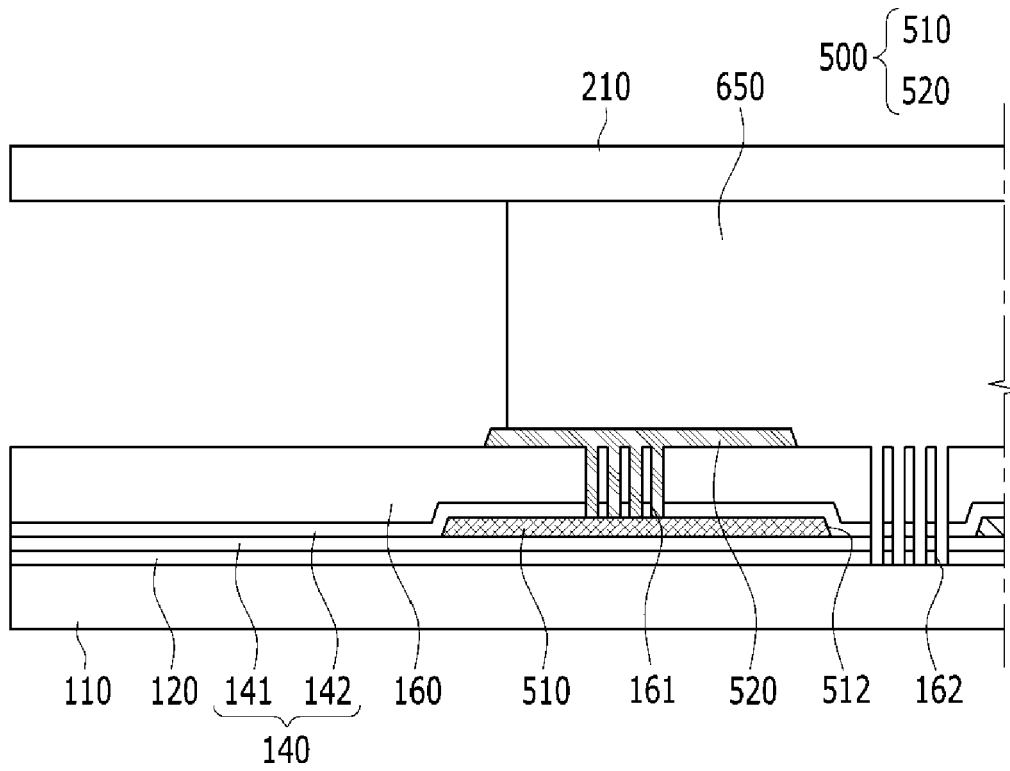


FIG. 16

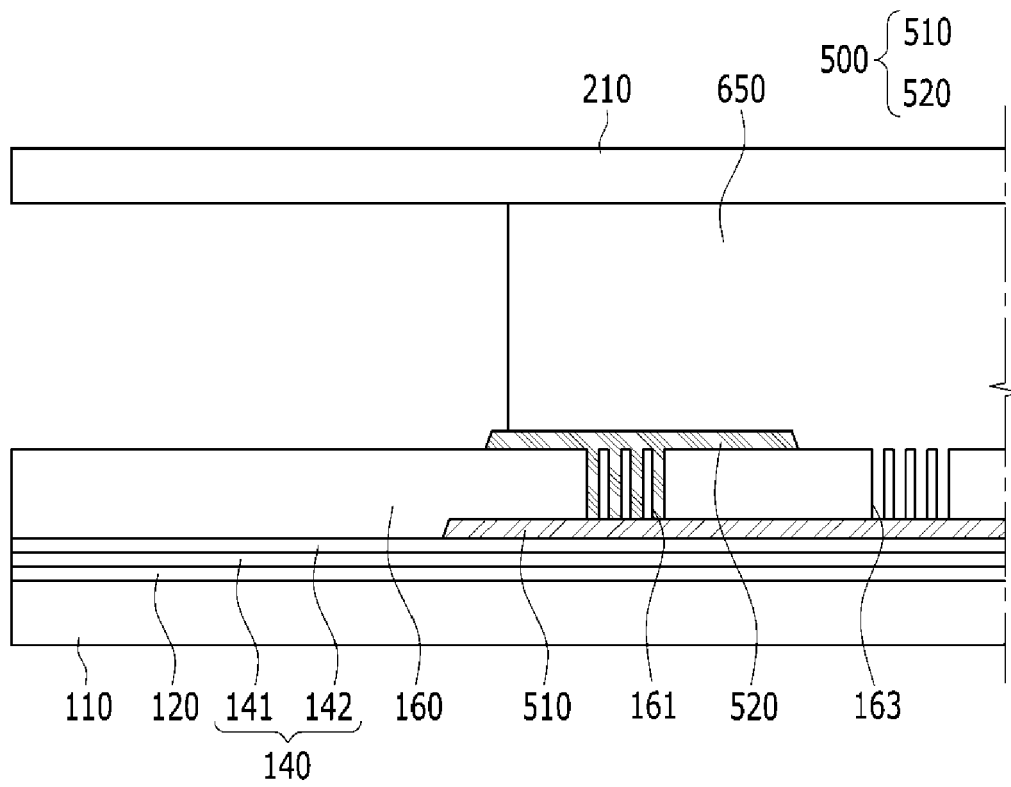


FIG. 17

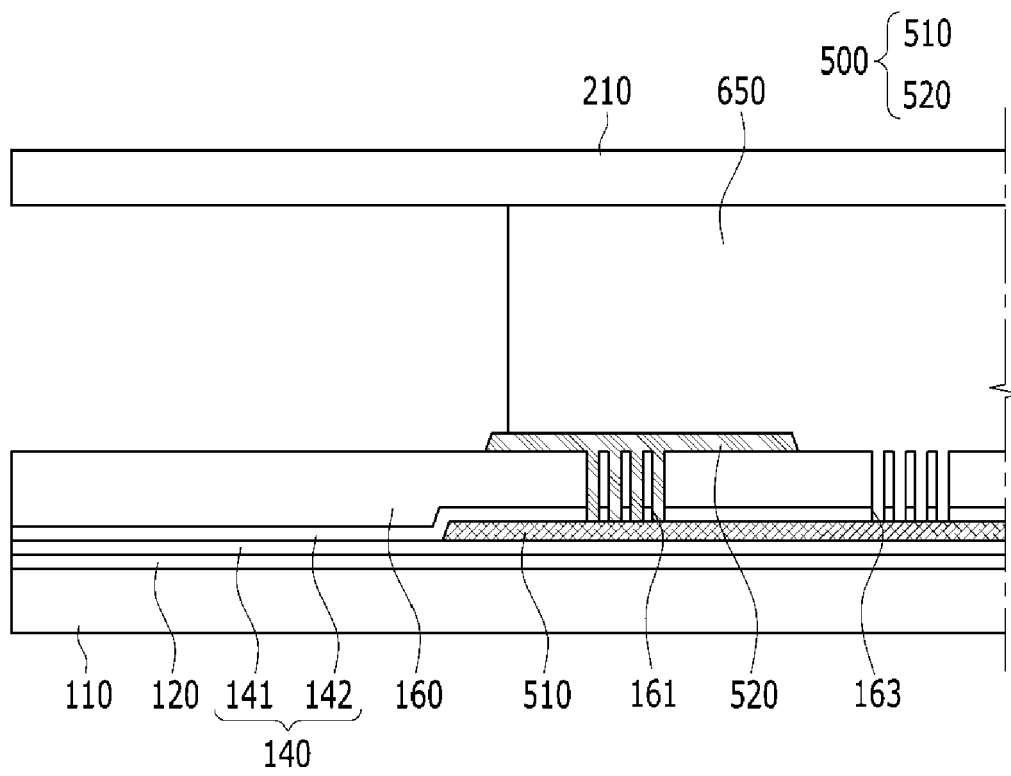
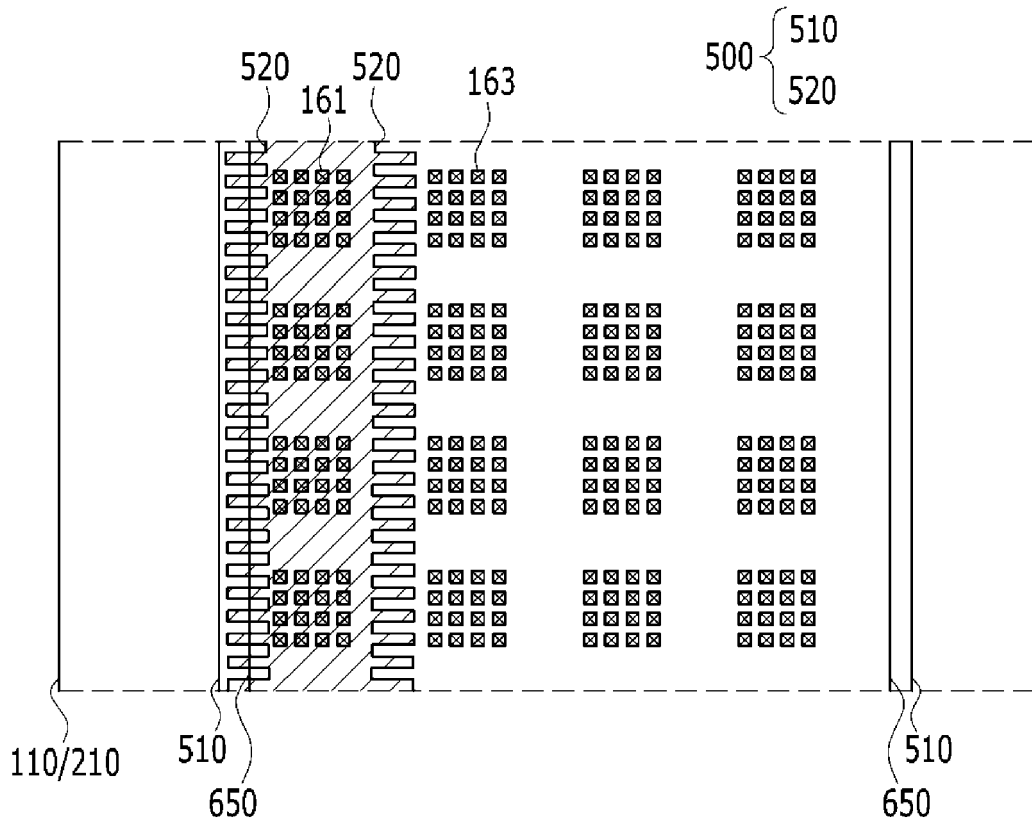


FIG. 18





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Application Number
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Y	* figures 1-5 * * paragraphs [0006], [0008], [0010], [0011], [0015], [0040], [0043] - [0046], [0048] - [0050], [0052], [0057], [0060], [0063] - [0065], [0080] - [0084] *	3,4,7,8,14,15	ADD. H01L27/32
X	US 2015/060789 A1 (CHO SUNG-HO [KR] ET AL) 5 March 2015 (2015-03-05)	1,2,5,6,9-13	
Y	* figure 3 * * paragraphs [0010], [0049], [0050], [0058] - [0060], [0063], [0064] *	3,4,7,8,14,15	
Y	US 2015/270287 A1 (KIM KWANG MIN [KR] ET AL) 24 September 2015 (2015-09-24)	3,4,14,15	
Y	* paragraphs [0050], [0051], [0053], [0055], [0076], [0079] *		
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	* figure 6 * * paragraphs [0054] - [0055] *		
The present search report has been drawn up for all claims			
Place of search The Hague		Date of completion of the search 8 September 2017	Examiner De Laere, Ann
CATEGORY OF CITED DOCUMENTS X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document			

EPO FORM 1503 03/02 (P04C01)

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ON EUROPEAN PATENT APPLICATION NO.

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08-09-2017

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For more details about this annex : see Official Journal of the European Patent Office, No. 12/82

专利名称(译)	有机发光二极管显示装置		
公开(公告)号	EP3232489A1	公开(公告)日	2017-10-18
申请号	EP2017166924	申请日	2017-04-18
[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	PARK KYUNG MIN SO DONG YOON		
发明人	PARK, KYUNG MIN SO, DONG-YOON		
IPC分类号	H01L51/52 H01L27/32		
CPC分类号	H01L27/3276 H01L27/3279 H01L51/5246 H01L51/5253 H01L27/3246 H01L27/3251		
优先权	1020160046265 2016-04-15 KR		
外部链接	Espacenet		

摘要(译)

有机发光装置包括：第一基板，包括显示区域和非显示区域；以及虚设金属层，设置在非显示区域中的第一基板上。虚设金属层包括彼此重叠的第一虚设金属层（510）和第二虚设金属层（520）。有机发光装置还包括在横截面图中设置在第一虚设金属层和第二虚设金属层之间的绝缘层（160），覆盖第一基板的第二基板（210）和密封剂（650）设置在第一基板和第二基板之间并与虚设金属层重叠。第一虚设金属层电连接到第二虚设金属层，并且密封剂接触第二虚设金属层。

FIG. 1

